Kodak

DEVICE
PERFORMANCE
SPECIFICATION

KODAK KAI-4020
KODAK KAI-4020M
KODAK KAI-4020CM
Image Sensor

2048 (H) x 2048 (V)
Interline Transfer
Progressive Scan CCD

December 16, 2003
Revision 2.0

www.kodak.com/go/imagers 585-722-4385 Email: imagers@kodak.com

TABLE OF CONTENTS

TABLE OF FIGURES **4**

DEVICE DESCRIPTION **6**

ARCHITECTURE 6
OVERALL 6
Pixel *7*
Vertical to Horizontal Transfer *8*
Horizontal Register to Floating Diffusion *9*
Horizontal Register Split *10*
Single Output Operation *10*
Dual Output Operation *10*
Output *11*
ESD Protection *12*
PHYSICAL DESCRIPTION 13
Pin Description and Device Orientation *13*

PERFORMANCE **14**

POWER - ESTIMATED 14
FRAME RATES 14
IMAGING PERFORMANCE 15
Image Performance Operational Conditions *15*
Imaging Performance Specifications *15*
Defect Definitions *18*
Defect Map *18*
Quantum Efficiency *19*
Angular Quantum Efficiency *20*
Dark Current versus Temperature *21*

TEST DEFINITIONS **22**

TEST REGIONS OF INTEREST 22
OVERCLOCKING 22
Tests *23*

OPERATION **25**

MAXIMUM RATINGS 25
DC BIAS OPERATING CONDITIONS 25
AC OPERATING CONDITIONS 26
Clock Levels *26*
Clock Line Capacitances *27*
TIMING REQUIREMENTS 28
TIMING MODES 29
Progressive Scan *29*
Summed Interlaced Scan *30*
Non-Summed Interlaced Scan *31*
FRAME TIMING 32
Frame Timing without Binning - Progressive Scan *32*
Frame Timing for Vertical Binning by 2 - Progressive Scan *32*
Frame Timing Non-Summed Interlaced Scan *33*
Frame Timing Summed Interlaced Scan *35*
Frame Timing Edge Alignment *37*
LINE TIMING 38
Line Timing Single Output – Progressive Scan *38*

Line Timing Dual Output – Progressive Scan *38*
Line Timing Vertical Binning by 2 – Progressive Scan *39*
Line Timing Detail – Progressive Scan *40*
Line Timing Binning by 2 Detail – Progressive Scan *40*
Line Timing Interlaced Modes *41*
Line Timing Edge Alignment *42*
PIXEL TIMING 43
Pixel Timing Detail *43*
FAST LINE DUMP TIMING 44
ELECTRONIC SHUTTER 45
Electronic Shutter Line Timing *45*
Electronic Shutter – Integration Time Definition *45*
Electronic Shutter Description *46*
LARGE SIGNAL OUTPUT 46

STORAGE AND HANDLING 47

STORAGE CONDITIONS 47
SOLDERING RECOMMENDATIONS 47

MECHANICAL DRAWINGS 48

PACKAGE 48
DIE TO PACKAGE ALIGNMENT 49
GLASS 50
GLASS TRANSMISSION 51

QUALITY ASSURANCE AND RELIABILITY 52

ORDERING INFORMATION 53

AVAILABLE PART CONFIGURATIONS 53

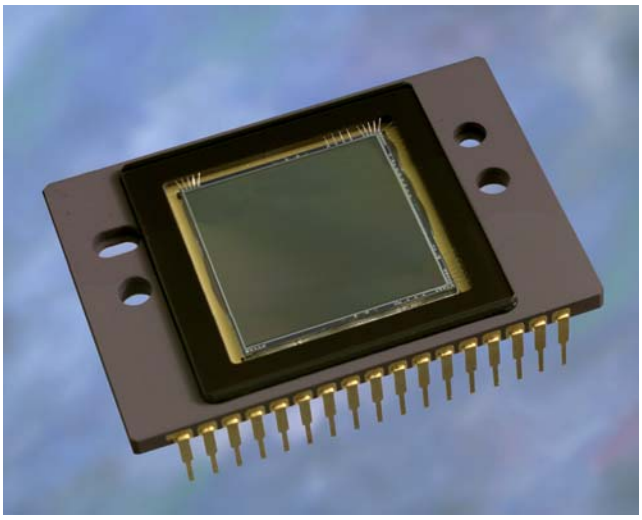
REVISION CHANGES 54

TABLE OF FIGURES

Figure 1 - Sensor Architecture 6
Figure 2 - Pixel Architecture 7
Figure 3 - Vertical to Horizontal Transfer Architecture 8
Figure 4 - Horizontal Register to Floating Diffusion Architecture 9
Figure 5 - Horizontal Register 10
Figure 6 - Output Architecture 11
Figure 7 - ESD Protection 12
Figure 8 - Power 14
Figure 9 - Frame Rates 14
Figure 10 - Monochrome Quantum Efficiency 19
Figure 11 - Color Quantum Efficiency 19
Figure 12 - Ultraviolet Quantum Efficiency 20
Figure 13 - Angular Quantum Efficiency 20
Figure 14 - Dark Current versus Temperature 21
Figure 15 - Overclock Regions of Interest 22
Figure 16 - Clock Line Capacitances 27
Figure 17 - Framing Timing without Binning 32
Figure 18 - Frame Timing for Vertical Binning by 2 32
Figure 19 - Non-Summed Interlaced Scan Even Frame Timing 33
Figure 20 - Non-Summed Interlaced Scan Odd Frame Timing 34
Figure 21 - Summed Interlaced Scan Even Frame Timing 35
Figure 22 - Summed Interlaced Scan Odd Frame Timing 36
Figure 23 - Frame Timing Edge Alignment 37
Figure 24 - Line Timing Single Output 38
Figure 25 - Line Timing Dual Output 38
Figure 26 - Line Timing Vertical Binning by 2 39
Figure 27 - Line Timing Detail 40
Figure 28 - Line Timing by 2 Detail 40
Figure 29 - Line Timing Interlaced Modes 41
Figure 30 - Line Timing Edge Alignment 42
Figure 31 - Pixel Timing 43
Figure 32 - Pixel Timing Detail 43
Figure 33 - Fast Line Dump Timing 44
Figure 34 - Electronic Shutter Line Timing 45
Figure 35 - Integration Time Definition 45
Figure 36 - Package Drawing 48
Figure 37 - Die to Package Alignment 49
Figure 38 - Glass Drawing 50
Figure 39 - Glass Transmission 51

SUMMARY SPECIFICATION

KODAK KAI-4020 Image Sensor 2048 (H) x 2048 (V) Interline Transfer Progressive Scan CCD



Description

The Kodak KAI-4020 Image Sensor is a high-performance 4-million pixel sensor designed for a wide range of medical, scientific and machine vision applications. The 7.4 µm square pixels with microlenses provide high sensitivity and the large full well capacity results in high dynamic range. The two high-speed outputs and binning capabilities allow for 16-50 frames per second (fps) video rate for the progressively scanned images. The vertical overflow drain structure provides antiblooming protection and enables electronic shuttering for precise exposure control. Other features include low dark current, negligible lag and low smear.

Parameter	Value
Architecture	Interline CCD; Progressive Scan
Total Number of Pixels	2112 (H) x 2072 (V) = approx. 4.38M
Number of Effective Pixels	2056 (H) x 2062 (V) = approx. 4.24M
Number of Active Pixels	2048 (H) x 2048 (V) = approx. 4.19M
Number of Outputs	1 or 2
Pixel Size	7.4µm (H) x 7.4µm (V)
Imager Size	21.43mm (diagonal)
Chip Size	16.67mm (H) x 16.05mm (V)
Aspect Ratio	1:1
Saturation Signal	40,000 e
Peak Quantum Efficiency (KAI-4020M)	55%
Peak Quantum Efficiency (KAI-4020CM) RGB	45%, 42%, 35%
Output Sensitivity	31 µV/e
Total System Noise (at 40MHZ)	25 e
Total System Noise (at 20MHz)	12 e
Dark Current	< 0.5 nA/cm2
Dark Current Doubling Temperature	7°C
Dynamic Range	60 dB
Charge Transfer Efficiency	> 0.99999
Blooming Suppression	300X
Smear	80 dB
Image Lag	<10 e
Maximum Data Rate	40 MHz

All parameters above are specified at T = 40*C

REVISION NO.: 2.0
EFFECTIVE DATE: December 19, 2003

DEVICE DESCRIPTION

Architecture

Overall

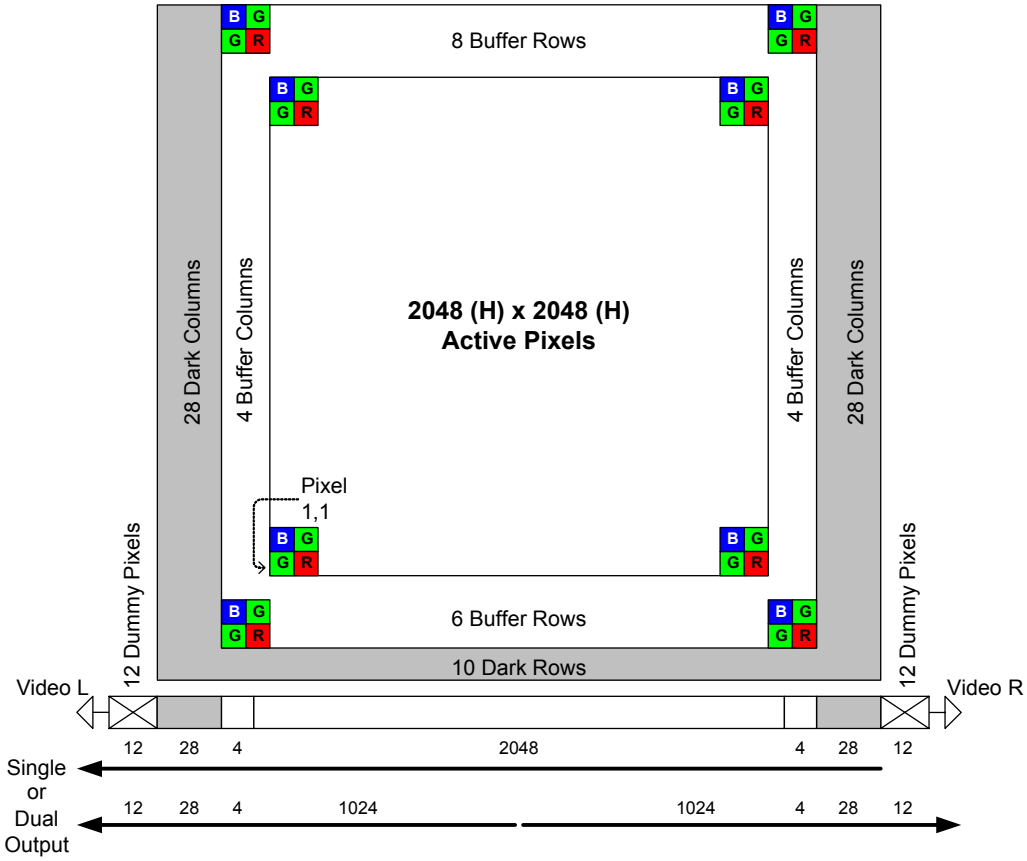


Figure 1 - Sensor Architecture

There are 10 light shielded rows followed 2062 photoactive rows. The first 6 and the last 8 photoactive rows are buffer rows giving a total of 2048 lines of image data.

In the single output mode all pixels are clocked out of the Video L output in the lower left corner of the sensor. The first 12 empty pixels of each line do not receive charge from the vertical shift register. The next 28 pixels receive charge from the left light shielded edge followed by 2056 photosensitive pixels and finally 28 more light shielded pixels from the right edge of the sensor. The first and last 4 photosensitive pixels are buffer pixels giving a total of 2048 pixels of image data.

In the dual output mode the clocking of the right half of the horizontal CCD is reversed. The left half of the image is clocked out Video L and the right half of the image is clocked out Video R. Each row consists of 12 empty pixels followed by 28 light shielded pixels followed by 1028 photosensitive pixels. When reconstructing the image, data from Video R will have to be reversed in a line buffer and appended to the Video L data.

There are no dark reference rows at the top and 10 dark rows at the bottom of the image sensor. The 10 dark rows are not entirely dark and so should not be used for a dark reference level. Use the 28 dark columns on the left or right side of the image sensor as a dark reference.

Of the 28 dark columns, the first and last dark columns should not be used for determining the zero signal level. Some light does leak into the first and last dark columns. Only use the center 26 columns of the 28 column dark reference.

Pixel

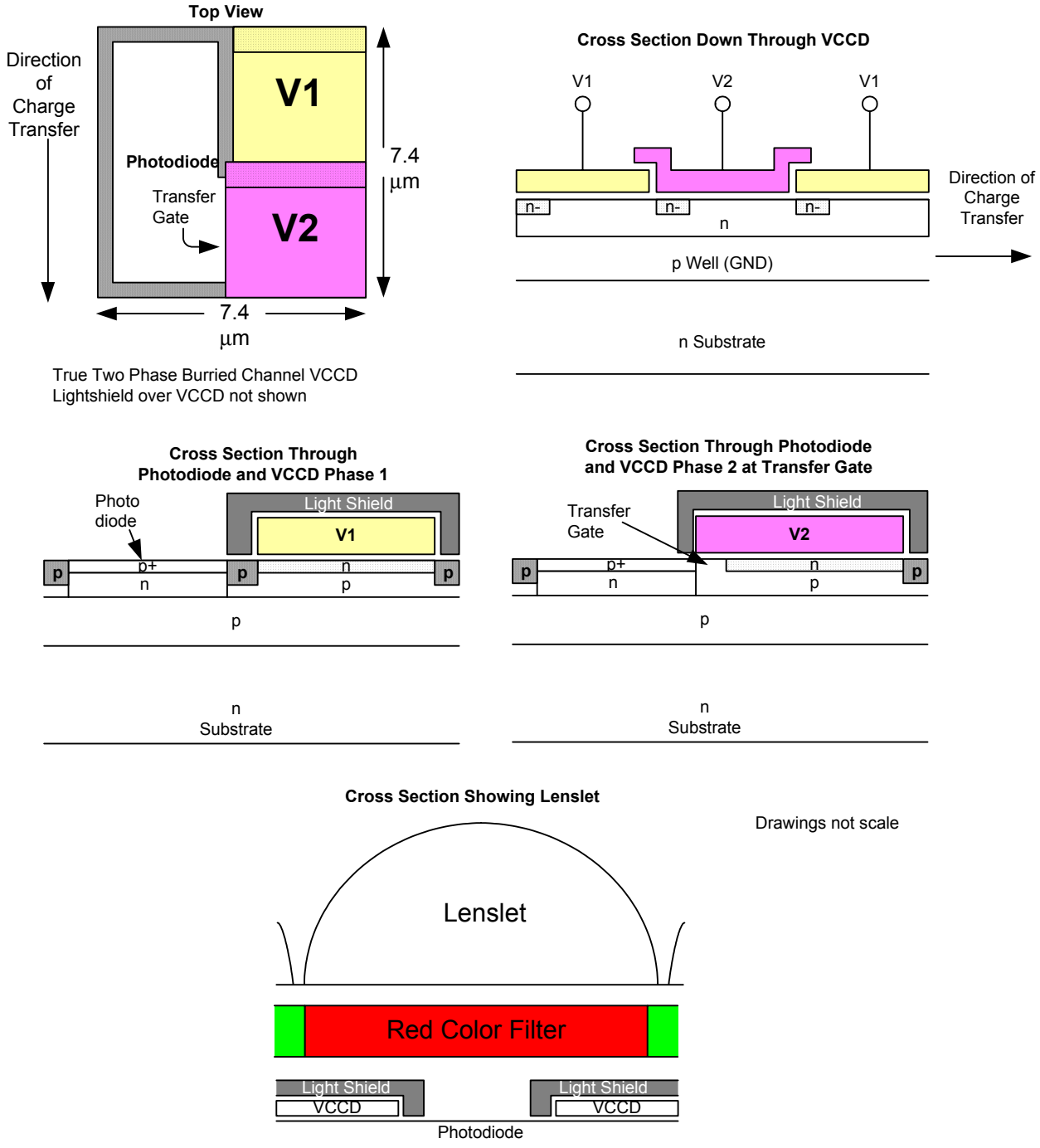


Figure 2 - Pixel Architecture

An electronic representation of an image is formed when incident photons falling on the sensor plane create electron-hole pairs within the individual silicon photodiodes. These photoelectrons are collected locally by the formation of potential wells at each photosite. Below photodiode saturation, the number of photoelectrons collected at each pixel is linearly dependant upon light level and exposure time and non-linearly dependant on wavelength. When the photodiodes charge capacity is reached, excess electrons are discharged into the substrate to prevent blooming.

Vertical to Horizontal Transfer

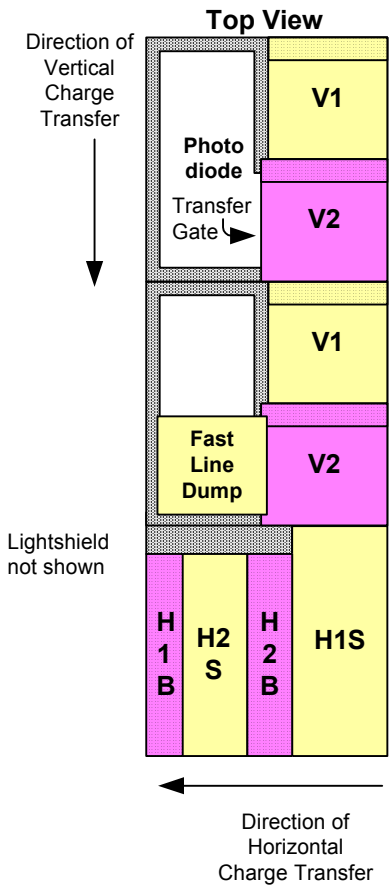


Figure 3 - Vertical to Horizontal Transfer Architecture

When the V1 and V2 timing inputs are pulsed, charge in every pixel of the VCCD is shifted one row towards the HCCD. The last row next to the HCCD is shifted into the HCCD. When the VCCD is shifted, the timing signals to the HCCD must be stopped. H1 must be stopped in the high state and H2 must be stopped in the low state. The HCCD clocking may begin THD µs after the falling edge of the V1 and V2 pulse.

Charge is transferred from the last vertical CCD phase into the H1S horizontal CCD phase. Refer to Figure 27 for an example of timing that accomplishes the vertical to horizontal transfer of charge.

If the fast line dump is held at the high level (FDH) during a vertical to horizontal transfer, then the entire line is removed and not transferred into the horizontal register.

Horizontal Register to Floating Diffusion

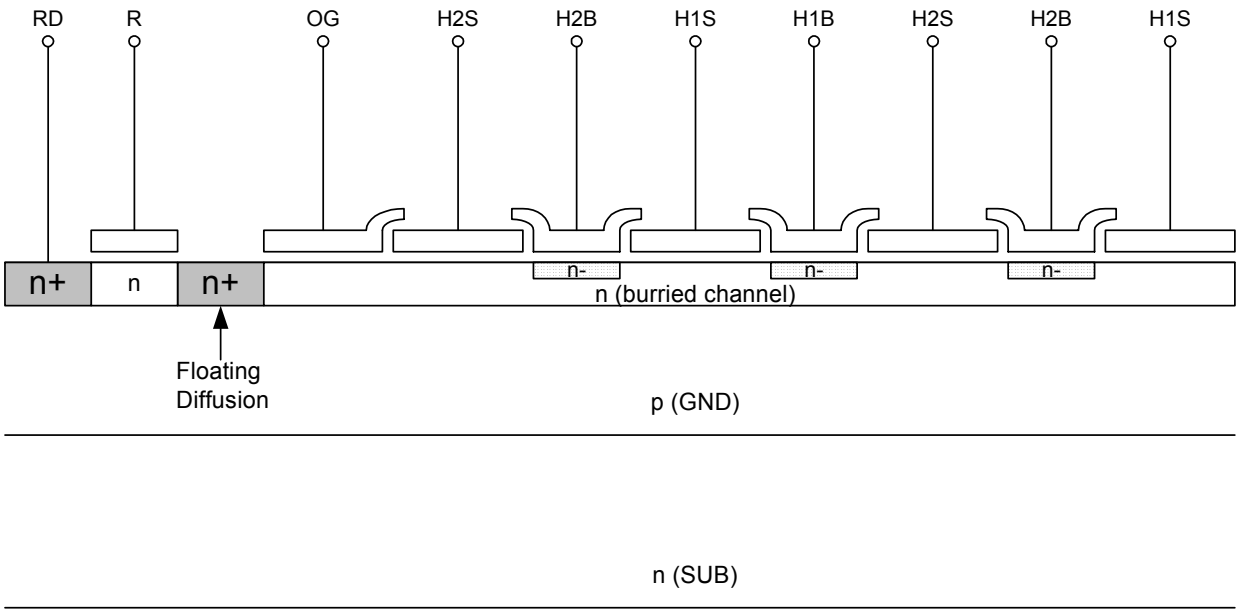


Figure 4 - Horizontal Register to Floating Diffusion Architecture

The HCCD has a total of 2124 pixels. The 2112 vertical shift registers (columns) are shifted into the center 2112 pixels of the HCCD. There are 12 pixels at both ends of the HCCD, which receive no charge from a vertical shift register. The first 12 clock cycles of the HCCD will be empty pixels (containing no electrons). The next 28 clock cycles will contain only electrons generated by dark current in the VCCD and photodiodes. The next 2056 clock cycles will contain photo-electrons (image data). Finally, the last 28 clock cycles will contain only electrons generated by dark current in the VCCD and photodiodes. Of the 28 dark columns, the first and last dark columns should not be used for determining the zero signal level. Some light does leak into the first and last dark columns. Only use the center 26 columns of the 28 column dark reference.

When the HCCD is shifting valid image data, the timing inputs to the electronic shutter (SUB), VCCD (V1, V2), and fast line dump (FD) should be not be pulsed. This prevents unwanted noise from being introduced. The HCCD is a type of charge coupled device known as a pseudo-two phase CCD. This type of CCD has the ability to shift charge in two directions. This allows the entire image to be shifted out to the video L output, or to the video R output (left/right image reversal). The HCCD is split into two equal halves of 1068 pixels each. When operating the sensor in single output mode the two halves of the HCCD are shifted in the same direction. When operating the sensor in dual output mode the two halves of the HCCD are shifted in opposite directions. The direction of charge transfer in each half is controlled by the H1BL, H2BL, H1BR, and H2BR timing inputs.

Horizontal Register Split

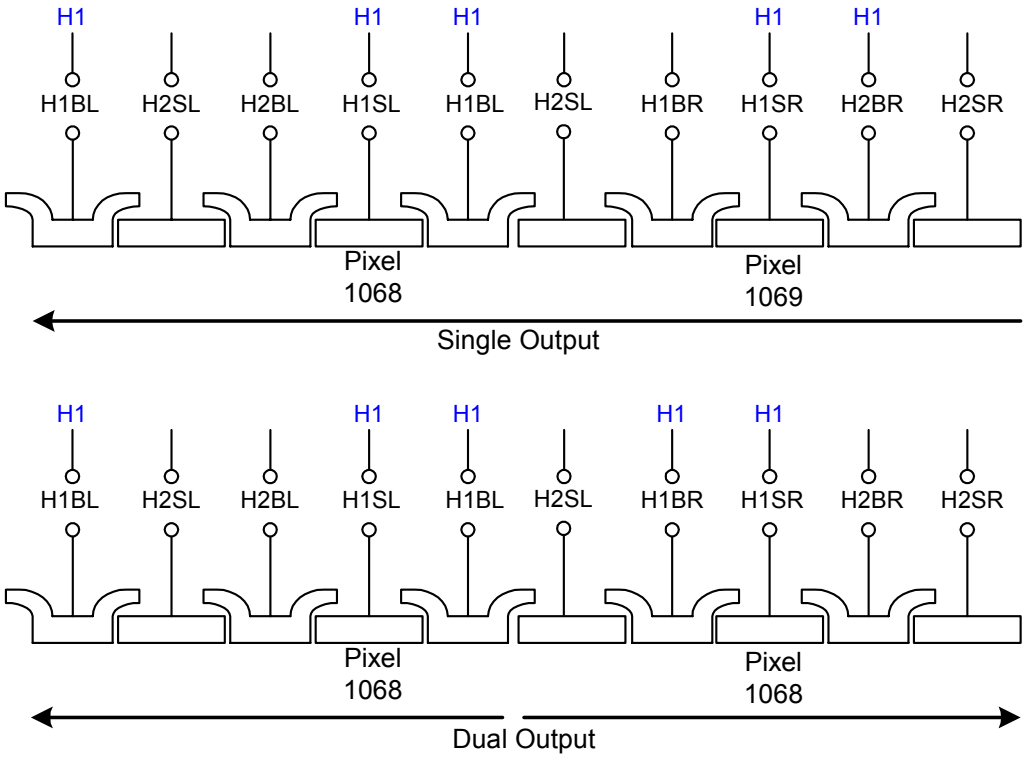


Figure 5 - Horizontal Register

Single Output Operation

When operating the sensor in single output mode all pixels of the image sensor will be shifted out the Video L output (pin 12). To conserve power and lower heat generation the output amplifier for Video R may be turned off by connecting VDDR (pin 24) and VOUTR (pin 23) to GND (zero volts).

The H1 timing from the timing diagrams should be applied to H1SL, H1BL, H1SR, H2BR, and the H2 timing should be applied to H2SL, H2BL, H2SR, and H1BR. In other words, the clock driver generating the H1 timing should be connected to pins 16, 15, 19, and 21. The clock driver generating the H2 timing should be connected to pins 17, 14, 18, and 20. The horizontal CCD should be clocked for 12 empty pixels plus 28 light shielded pixels plus 2056 photoactive pixels plus 28 light shielded pixels for a total of 2124 pixels.

Dual Output Operation

In dual output mode the connections to the H1BR and H2BR pins are swapped from the single output mode to change the direction of charge transfer of the right side horizontal shift register. In dual output mode both VDDL and VDDR (pins 11, 24) should be connected to 15 V. The H1 timing from the timing diagrams should be applied to H1SL, H1BL, H1SR, H1BR, and the H2 timing should be applied to H2SL, H2BL, H2SR, and H2BR. The clock driver generating the H1 timing should be connected to pins 16, 15, 19, and 20. The clock driver generating the H2 timing should be connected to pins 17, 14, 18, and 21. The horizontal CCD should be clocked for 12 empty pixels plus 28 light shielded pixels plus 1028 photoactive pixels for a total of 1068 pixels. If the camera is to have the option of dual or single output mode, the clock driver signals sent to H1BR and H2BR may be swapped by using a relay. Another alternative is to have two extra clock drivers for H1BR and H2BR and invert the signals in the timing logic generator. If two extra clock drivers are used, care must be taken to ensure the rising and falling edges of the H1BR and H2BR clocks occur at the same time (within 3ns) as the other HCCD clocks.

Output

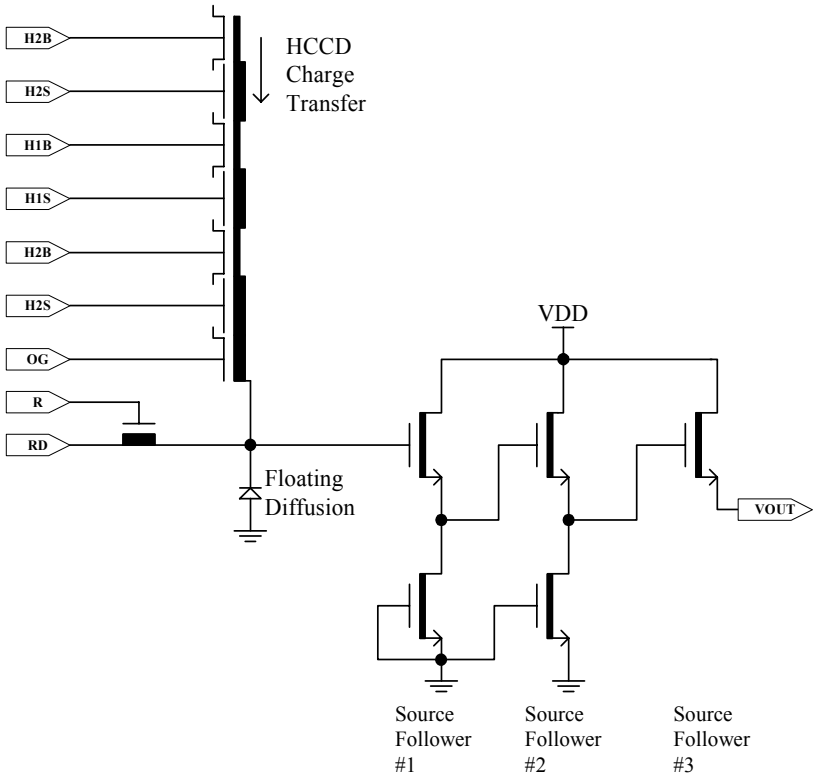


Figure 6 - Output Architecture

Charge packets contained in the horizontal register are dumped pixel by pixel onto the floating diffusion (fd) output node whose potential varies linearly with the quantity of charge in each packet. The amount of potential charge is determined by the expression $\Delta Vfd=\Delta Q/Cfd$. A three-stage source-follower amplifier is used to buffer this signal voltage off chip with slightly less than unity gain. The translation from the charge domain to the voltage domain is quantified by the output sensitivity or charge to voltage conversion in terms of microvolts per electron ($\mu V/e^-$). After the signal has been sampled off chip, the reset clock (R) removes the charge from the floating diffusion and resets its potential to the reset drain voltage (RD).

When the image sensor is operated in the binned or summed interlaced modes there will be more than 20,000 electrons in the output signal. The image sensor is designed with a 31µV/e charge to voltage conversion on the output. This means a full signal of 20,000 electrons will produce a 640 mV change on the output amplifier. The output amplifier was designed to handle an output swing of 640 mV at a pixel rate of 40 MHz. If 40,000 electron charge packets are generated in the binned or summed interlaced modes then the output amplifier output will have to swing 1280 mV. The output amplifier does not have enough bandwidth (slew rate) to handle 1280 mV at 40 MHz. Hence, the pixel rate will have to be reduced to 20 MHz if the full dynamic range of 40,000 electrons is desired.

The charge handling capacity of the output amplifier is also set by the reset clock voltage levels. The reset clock driver circuit is very simple if an amplitude of 5 V is used. But the 5 V amplitude restricts the output amplifier charge capacity to 20,000 electrons. If the full dynamic range of 40,000 electrons is desired then the reset clock amplitude will have to be increased to 7 V.
If you only want a maximum signal of 20,000 electrons in binned or summed interlaced modes, then a 40 MHz pixel rate with a 5 V reset clock may be used. The output of the amplifier will be unpredictable above 20,000 electrons so be sure to set the maximum input signal level of your analog to digital converter to the equivalent of 20,000 electrons (640 mV).

ESD Protection

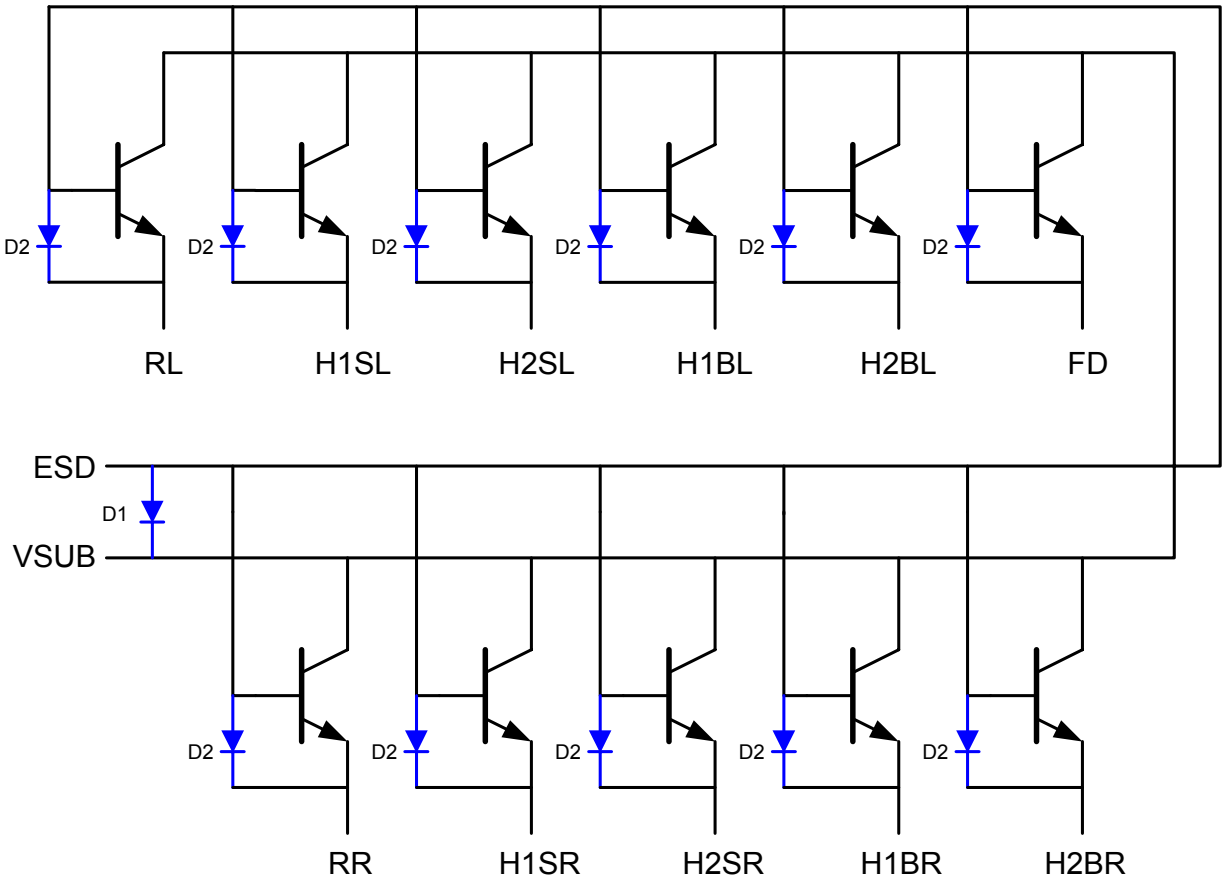


Figure 7 - ESD Protection

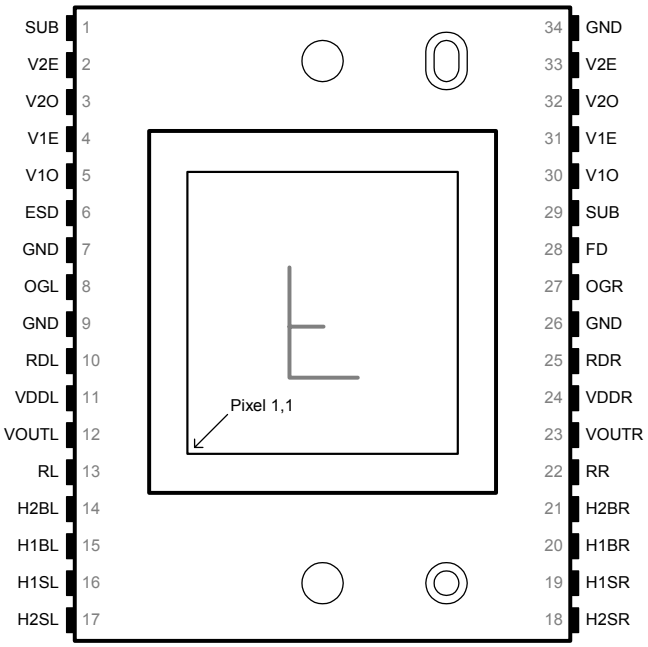
The ESD protection on the KAI-4020 is implemented using bipolar transistors. The substrate (VSUB) forms the common collector of all the ESD protection transistors. The ESD pin is the common base of all the ESD protection transistors. Each protected pin is connected to a separate emitter as shown in Figure 7 - ESD Protection.

The ESD circuit turns on if the base-emitter junction voltage exceeds 17 V. Care must be taken while operating the image sensor, especially during the power on sequence, to not forward bias the base-emitter or base-collector junctions. If it is possible for the camera power up sequence to forward bias these junctions then diodes D1 and D2 should be added to protect the image sensor. Put one diode D1 between the ESD and VSUB pins. Put one diode D2 on each pin that may forward bias the base-emitter junction. The diodes will prevent large currents from flowing through the image sensor.

Note that diodes D1 and D2 are added external to the KAI-4020 CCD.

Physical Description

Pin Description and Device Orientation



Pin	Name	Description	Pin	Name	Description
1	SUB	Substrate	34	GND	Ground
2	V2E	Vertical Clock, Phase 2, Even	33	V2E	Vertical Clock, Phase 2, Even
3	V2O	Vertical Clock, Phase 2, Odd	32	V2O	Vertical Clock, Phase 2, Odd
4	V1E	Vertical Clock, Phase 1, Even	31	V1E	Vertical Clock, Phase 1, Even
5	V1O	Vertical Clock, Phase 1, Odd	30	V1O	Vertical Clock, Phase 1, Odd
6	ESD	ESD	29	SUB	Substrate
7	GND	Ground	28	FD	Fast Line Dump Gate
8	OGL	Output Gate, Left	27	OGR	Output Gate. Right
9	GND	Ground	26	GND	Ground
10	RDL	Reset Drain, Left	25	RDR	Reset Drain, Right
11	VDDL	Vdd, Left	24	VDDR	Vdd, Right
12	VOUTL	Video Output, Left	23	VOUTR	Video Output. Right
13	RL	Reset Gate, Left	22	RR	Reset Gate, Right
14	H2BL	H2 Barrier, Left	21	H2BR	H2 Barrier, Right
15	H1BL	H1 Barrier, Left	20	H1BR	H1 Barrier, Right
16	H1SL	H1 Storage, Left	19	H1SR	H1 Storage, Right
17	H2SL	H2 Storage, Left	18	H2SR	H2 Storage, Right

The pins are on a 0.07” spacing

PERFORMANCE

Power - Estimated

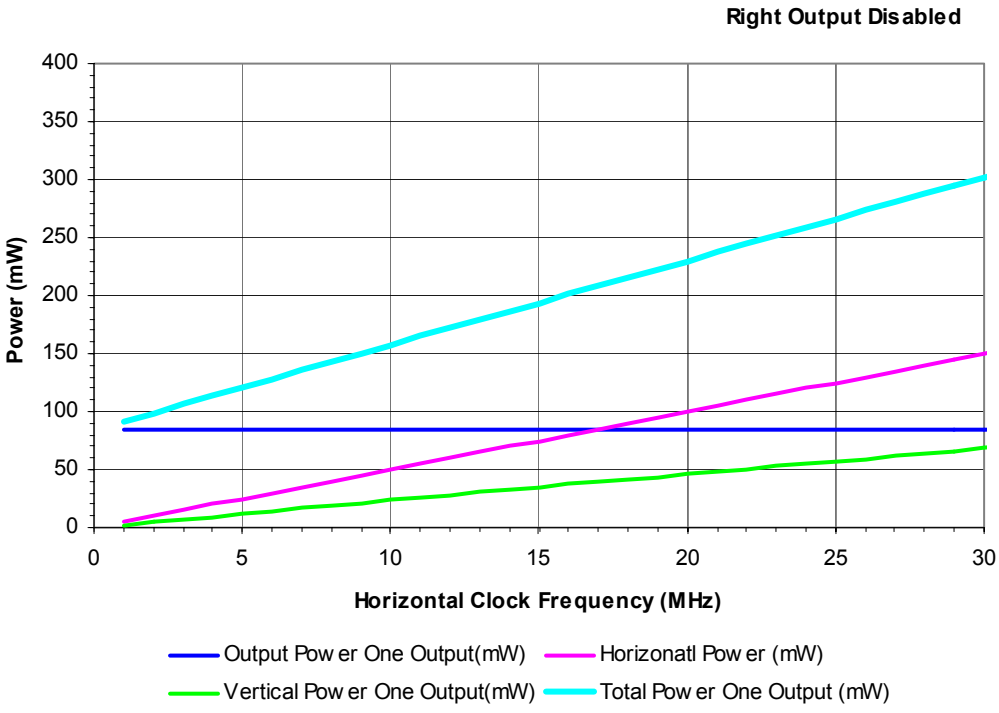


Figure 8 - Power

Frame Rates

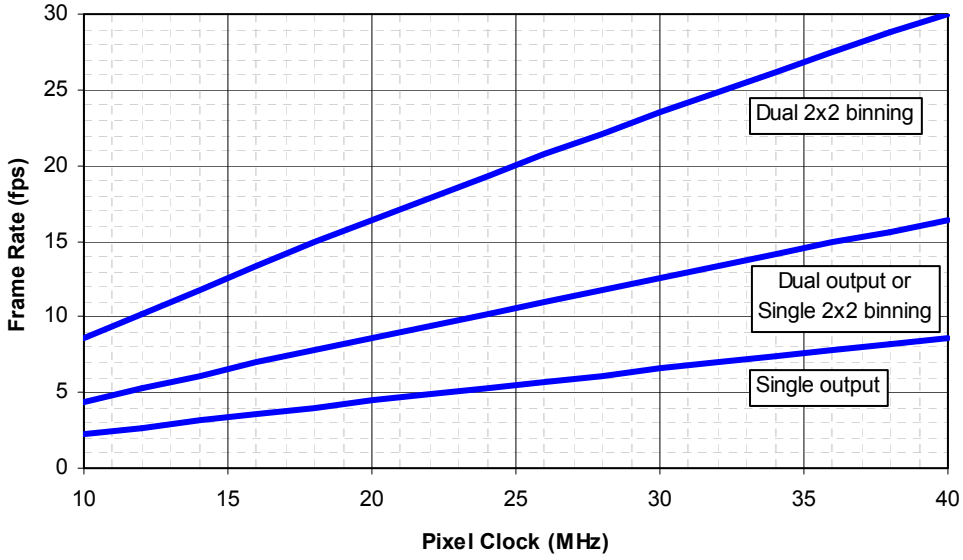


Figure 9 - Frame Rates

Imaging Performance

Image Performance Operational Conditions

Unless otherwise noted, the Imaging Performance Specifications are measured using the following conditions:

Description	Condition	Notes
Frame time	538 msec	1
Horizontal clock frequency	10 MHz	
Light source (LED)	Continuous red, green and blue illumination centered at 450, 530 an 650 nm	2,3
Operation	Nominal operating voltages and timing	

Notes:
1. Electronic shutter is not used. Integration time equals frame time.
2. LEDs used: Blue: Nichia NLPB500, Green: Nichia NSPG500S and Red: HP HLMP-8115.
3. For monochrome sensor, only green LED used.

Imaging Performance Specifications

KAI-4020M and KAI-4020CM

Description	Symbol	Min.	Nom.	Max.	Units	Sampling Plan	Temperature(s) Tested At (°C)	Notes	Test
Dark Center Uniformity		XXX	XXX	20	mVrms	Die	27, 40		1
Dark Global Uniformity		XXX	XXX	5.0	mVpp	Die	27, 40		2
Global Uniformity		XXX	2.5	5.0	%rms	Die	27, 40	1	3
Global Peak to Peak Uniformity	PRNU	XXX	10	20	%pp	Die	27, 40	1	4
Center Uniformity		XXX	1.0	2.0	%rms	Die	27, 40	1	5
Maximum Photoresponse Nonlinearity	NL	XXX	2		%	Design		2, 3	
Maximum Gain Difference Between Outputs	ΔG	XXX	10		%	Design		2, 3	
Max. Signal Error due to Nonlinearity Dif.	ΔNL	XXX	1		%	Design		2, 3	

Description (cont)	Symbol	Min.	Nom.	Max.	Units	Sampling Plan	Temperature(s) Tested At (°C)	Notes	Test
Horizontal CCD Charge Capacity	HNe		100		ke^-	Design			
Vertical CCD Charge Capacity	VNe	50	60		ke^-	Die			
Photodiode Charge Capacity	PNe	38	40		ke^-	Die			
Horizontal CCD Charge Transfer Efficiency	HCTE	0.99999		XXX		Design			
Vertical CCD Charge Transfer Efficiency	VCTE	0.99999		XXX		Design			
Photodiode Dark Current	Ipd	XXX	40	350	e/p/s	Die			
Photodiode Dark Current	Ipd	XXX	0.01	0.1	nA/cm^2	Die			
Vertical CCD Dark Current	Ivd	XXX	400	1711	e/p/s	Die			
Vertical CCD Dark Current	Ivd	XXX	0.12	0.5	nA/cm^2	Die			
Image Lag	Lag	XXX	<10	50	e^-	Design			
Antiblooming Factor	Xab	100	300	XXX					
Vertical Smear	Smr	XXX	80	75	DB				
Total Noise	n_{e-T}		12		e^-rms	Design		4	
Total Noise	n_{e-T}		25		e^-rms	Design		5	
Dynamic Range	DR		60		dB	Design		5, 6	
Output Amplifier DC Offset	V_{odc}	4	8.5	14	V	Die			
Output Amplifier Bandwidth	F_{-3db}		140		MHz	Design			
Output Amplifier Impedance	R_{OUT}	100	130	200	Ohms	Die			
Output Amplifier Sensitivity	$\Delta V/\Delta N$		31		$\mu V/e^-$	Design			

KAI-4020M

Description	Symbol	Min.	Nom.	Max.	Units	Sampling Plan	Temperature(s) Tested At (°C)	Notes	Test
Peak Quantum Efficiency	QE_{max}	45	55	XXX	%	Design			
Peak Quantum Efficiency Wavelength	λQE	XXX	500	XXX	nm	Design			

KAI-4020CM

Description	Symbol	Min.	Nom.	Max.	Units	Sampling Plan	Temperature(s) Tested At (°C)	Notes	Test
Peak Quantum Efficiency Red Green Blue	QE_{max}		45 42 35	XXX XXX XXX	%	Design			
Peak Quantum Efficiency Wavelength Red Green Blue	λQE		470 540 620	XXX XXX XXX	nm	Design			

Notes:
1. Per color.
2. Value is over the range of 10% to 90% of photodiode saturation.
3. Value is for the sensor operated without binning
4. Includes system electronics noise, dark pattern noise and dark current shot noise at 20 MHz.
5. Includes system electronics noise, dark pattern noise and dark current shot noise at 40 MHz.
6. Uses 20LOG(PNe/ n_{e-T})

Defect Definitions

Description	Definition	Maximum	Temperature(s) tested at (°C)	Notes	Test
Major dark field defective pixel	Defect >= 148 mV	40	27, 40	1	6
Major bright field defective pixel	Defect >= 10 %			1	7
Minor dark field defective pixel	Defect >= 76 mV	400	27, 40		6
Dead pixel	Defect >= 80 %	5	27, 40	1	7
Saturated pixel	Defect >= 340 mV	10	27, 40	1	6
Cluster defect	A group of 2 to 10 contiguous majo defective pixels, but no more than 2 adjacent defects horizontally	8	27, 40	1	
Column defect	A group of more than 10 contiguous major defective pixels along a single column	0	27,40	1	

Notes:
1. There will be at least two non-defective pixels separating any two major defective pixels.

Defect Map

The defect map supplied with each sensor is based upon testing at an ambient (27°C) temperature. Minor point defects are not included in the defect map. All pixels are referenced to pixel 1,1 in the defect map.

Quantum Efficiency

Monochrome Quantum Efficiency

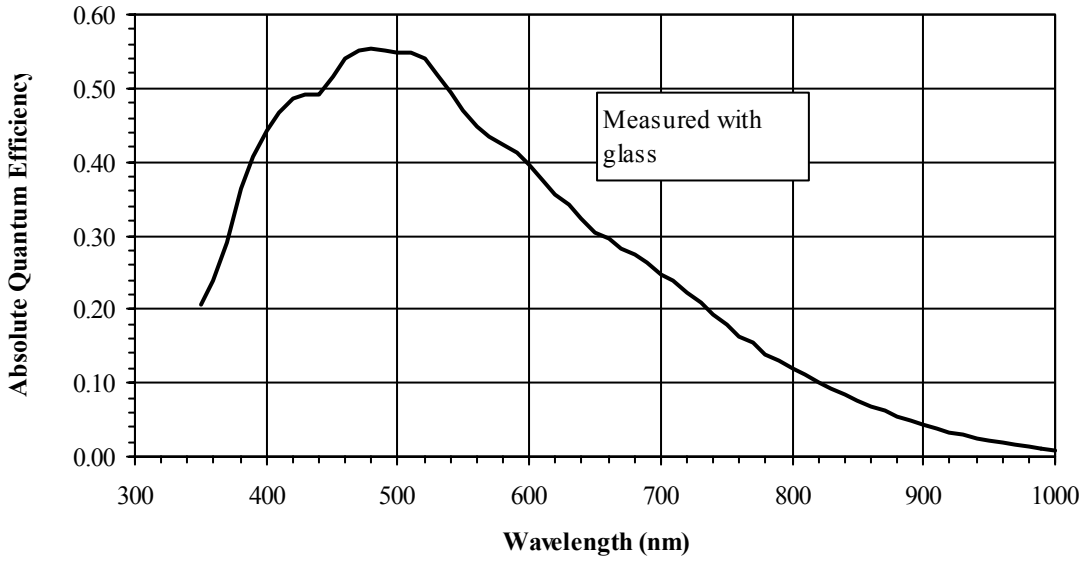


Figure 10 - Monochrome Quantum Efficiency

Color Quantum Efficiency

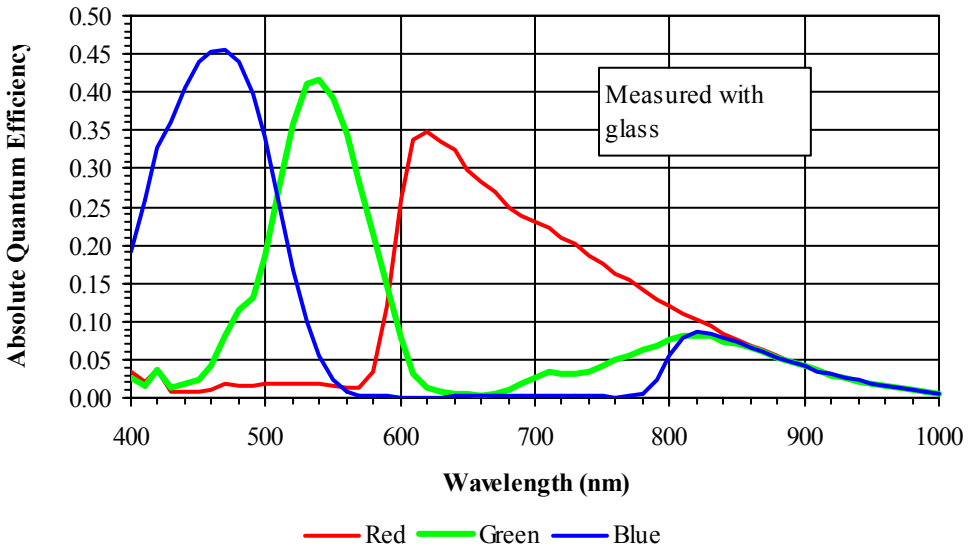


Figure 11 - Color Quantum Efficiency

Ultraviolet (UV) Quantum Efficiency

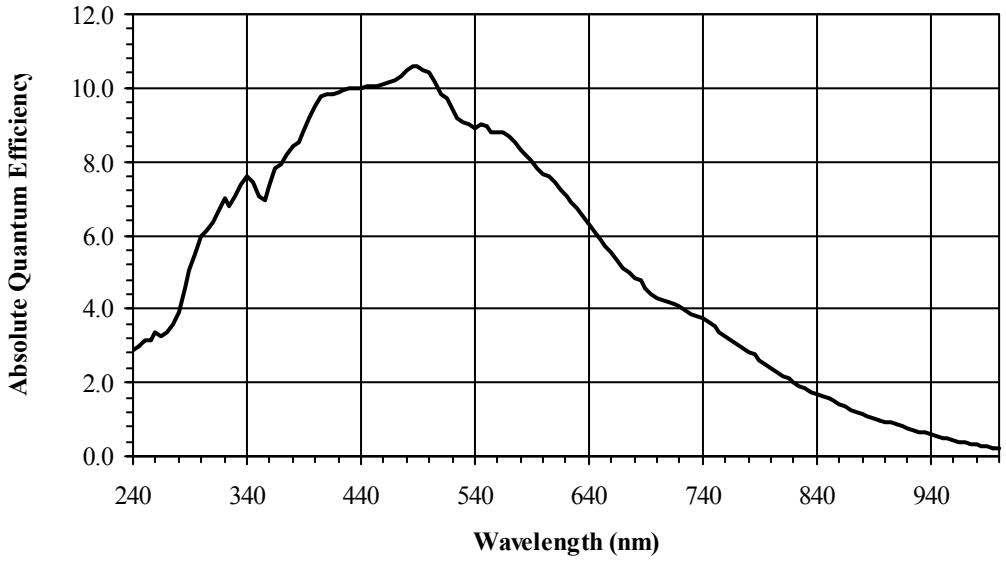


Figure 12 - Ultraviolet Quantum Efficiency

Angular Quantum Efficiency

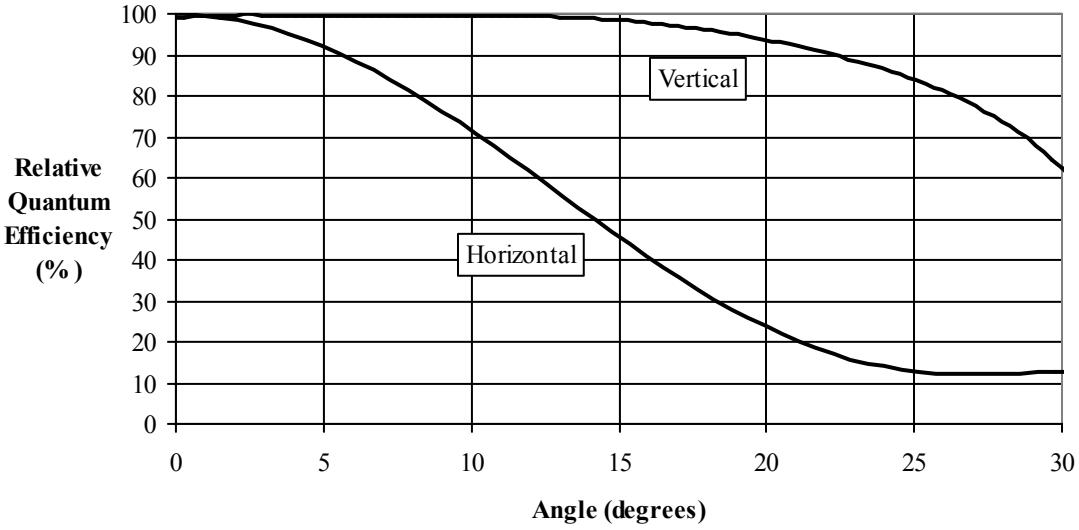


Figure 13 - Angular Quantum Efficiency

Dark Current versus Temperature

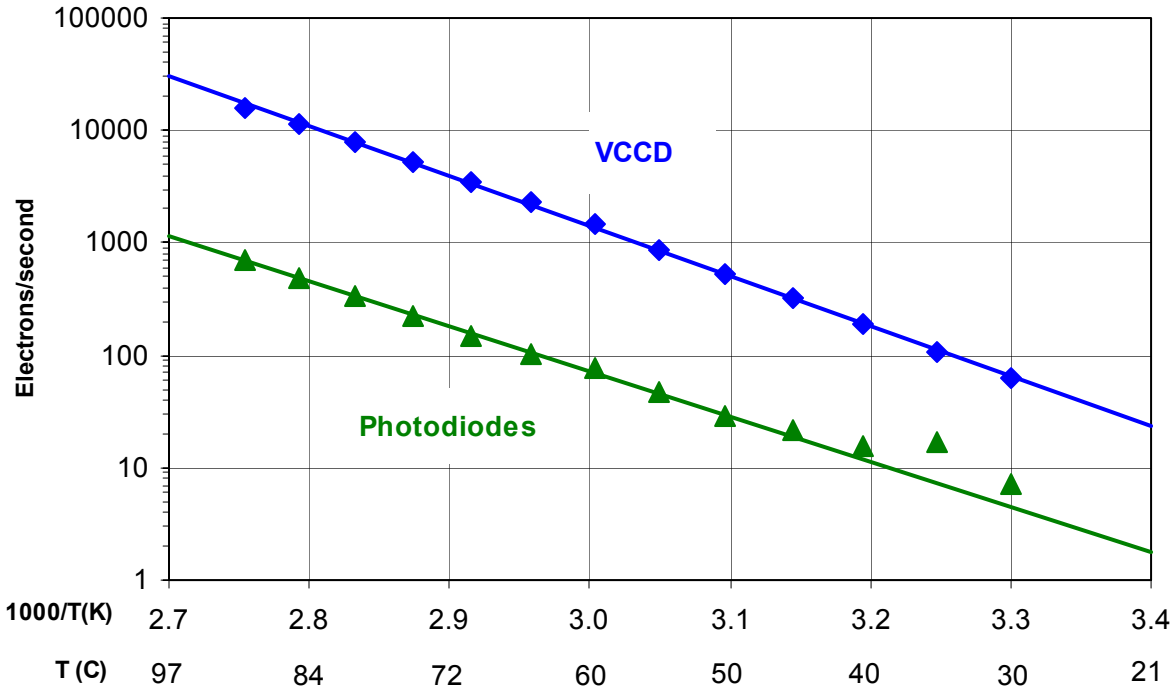


Figure 14 - Dark Current versus Temperature

TEST DEFINITIONS

Test Regions of Interest

Active Area ROI: Pixel 1, 1 to Pixel 2048,2048
Center 100 by 100 ROI: Pixel 974,974 to Pixel 1073,1073

Only the active pixels are used for performance and defect tests.

OverClocking

The test system timing is configured such that the sensor is overclocked in both the vertical and horizontal directions. See Figure 15 for a pictorial representation of the regions.

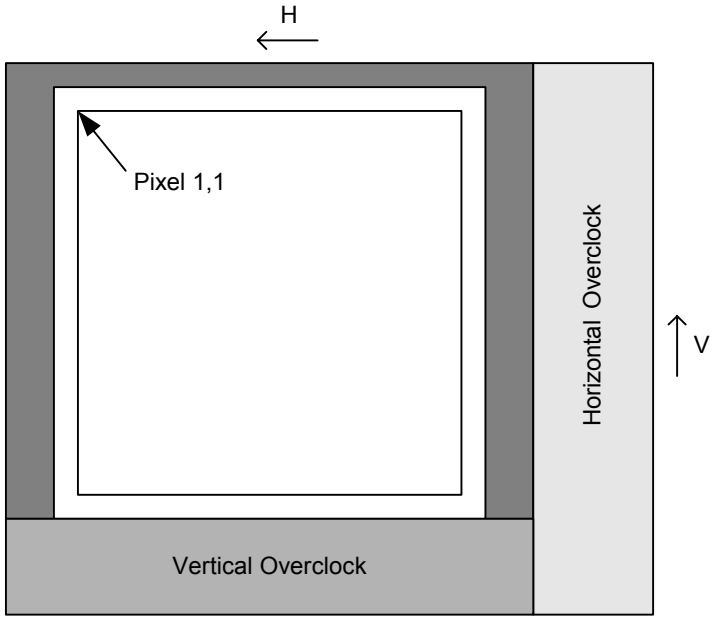


Figure 15 - Overclock Regions of Interest

Tests

1. **Dark Field Center Uniformity**
   This test is performed under dark field conditions. Only the center 100 by 100 pixels of the sensor are used for this test - pixel (974,974) to pixel (1073,1073).

$$\text{Dark field center uniformity} = \text{Standard Deviation of center 100 by 100 pixels in electrons} * \left(\frac{\text{DPS Integration time}}{\text{Actual integration time used}} \right)$$

   Units: e^- rms
   DPS integration time: Device Performance Specification Integration Time = 33 msec

2. **Dark Field Global Uniformity**
   This test is performed under dark field conditions. The sensor is partitioned into 256 sub regions of interest, each of which is 128 by 128 pixels in size. The average signal level of each of the 256 sub regions of interest is calculated. The signal level of each of the sub regions of interest is calculated using the following formula:

   Signal of ROI[i] = (ROI Average in ADU – Horizontal overclock average in ADU) * mV per count
   Where i = 1 to 256. During this calculation on the 256 sub regions of interest, the maximum and minimum signal levels are found.

   The dark field global uniformity is then calculated as the maximum signal found minus the minimum signal level found.

   Units: mVpp (millivolts peak to peak)

3. **Global Uniformity**
   This test is performed with the imager illuminated to a level such that the output is at 70% of saturation (approximately 450 mV). Prior to this test being performed the substrate voltage has been set such that the charge capacity of the sensor is TBD mV. Global uniformity is defined as

$$\text{Global Uniformity} = 100 * \left(\frac{\text{Active Area Standard Deviation}}{\text{Active Area Signal}} \right) \quad \text{Units: \%rms}$$

   Active Area Signal = Active Area Average – Horizontal Overclock Average

4. **Global Peak to Peak Uniformity**
   This test is performed with the imager illuminated to a level such that the output is at 70% of saturation (approximately 450 mV). Prior to this test being performed the substrate voltage has been set such that the charge capacity of the sensor is 450 mV. The sensor is partitioned into 256 sub regions of interest, each of which is 128 by 128 pixels in size. The average signal level of each of the 256 sub regions of interest (ROI) is calculated. The signal level of each of the sub regions of interest is calculated using the following formula:

   A[i] = (ROI Average – Horizontal Overclock Average)
   Where i = 1 to 256. During this calculation on the 256 sub regions of interest, the maximum and minimum average signal levels are found.

   The global peak to peak uniformity is then calculated as:

$$\text{Global Uniformity} = \frac{\text{A[i] Maximum Signal - A[i] Minimum Signal}}{\text{Active Area Signal}} \quad \text{Units: \%pp}$$

   Active Area Signal = Active Area Average – Horizontal Overclock Average

5. **Center Uniformity**
This test is performed with the imager illuminated to a level such that the output is at 70% of saturation (approximately 450 mV). Prior to this test being performed the substrate voltage has been set such that the charge capacity of the sensor is 450 mV. Defects are excluded for the calculation of this test. This test is performed on the center 100 by 100 pixels (See Test Regions of Interest) of the sensor. Center uniformity is defined as:

$$\text{Center ROI Uniformity} = 100 * \left(\frac{\text{Center ROI Standard Deviation}}{\text{Center ROI Signal}} \right) \quad \text{Units: \%rms}$$

Center ROI Signal = Center ROI Average – Horizontal Overclock Average

6. **Dark field defect test**
This test is performed under dark field conditions. The sensor is partitioned into 256 sub regions of interest, each of which is 128 by 128 pixels in size. In each region of interest, the median value of all pixels is found. For each region of interest, a pixel is marked defective if it is greater than or equal to the median value of that region of interest plus the defect threshold specified in “Defect Definitions” section.

7. **Bright field defect test**
This test is performed with the imager illuminated to a level such that the output is at 80% of saturation (approximately 32,000 electrons). Prior to this test being performed the substrate voltage has been set such that the charge capacity of the sensor is 40,000 electrons. The average signal level of all active pixels is found. The bright and dark thresholds are set as:
Dark defect threshold = Active Area Signal * threshold
Bright defect threshold = Active Area Signal * threshold

The sensor is then partitioned into 256 sub regions of interest, each of which is 128 by 128 pixels in size. In each region of interest, the average value of all pixels is found. For each region of interest, a pixel is marked defective if it is greater than or equal to the median value of that region of interest plus the bright threshold specified or if it is less than or equal to the median value of that region of interest minus the dark threshold specified.
Example for major bright field defective pixels:
- Average value of all active pixels is found to be 416 mV (32,000 electrons).
- Dark defect threshold: 416mV * 15% = 62.4 mV
- Bright defect threshold: 416mV * 15% = 62.4 mV
- Region of interest #1 selected. This region of interest is pixels 1,1 to pixels 128,128.
    - Median of this region of interest is found to be 416 mV.
    - Any pixel in this region of interest that is >= (416+62.4 mV) 478.4 mV in intensity will be marked defective.
    - Any pixel in this region of interest that is <= (416-62.4 mV) 353.6 mV in intensity will be marked defective.
- All remaining 255 sub regions of interest are analyzed for defective pixels in the same manner.

OPERATION

Maximum Ratings

Description	Symbol	Minimum	Maximum	Units	Notes
Temperature	T	-50	70	°C	1
Humidity	RH	5	90	%	2
Output Bias Current	Iout	0.0	10.0	mA	3
Off-chip Load	C_L		10	pF	4

Notes:
1. Noise performance will degrade at higher temperatures.
2. T=25ºC. Excessive humidity will degrade MTTF.
3. Total for both outputs. Current is 5 mA for each output. Note that the current bias affects the amplifier bandwidth.
4. With total output load capacitance of CL = 10pF between the outputs and AC ground.
5. Absolute maximum rating is defined as a level or condition that should not be exceeded at any time per the description. If the level or the condition is exceeded, the device will be degraded and may be damaged.

Caution: This device contains limited protection against Electrostatic Discharge (ESD)
Devices should be handled in accordance with strict ESD procedures for Class 0 devices (JESD22 Human Body Model) or Class A (Machine Model). Refer to Application Note MTD/PS-0224, “Electrostatic Discharge Control”

Caution: Improper cleaning of the cover glass may damage these devices.
Refer to Application Note MTD/PS-0237, “Cover Glass Cleaning for Image Sensors”

Caution: Each sensor is shipped with a protective tape on the cover glass. Care should be used when removing the tape to prevent ESD damage. The tape should be removed when the sensor is in the shipping container or when the sensor in a camera.

DC Bias Operating Conditions

Description	Symbol	Minimum	Nominal	Maximum	Units	Maximum DC Current (mA)	Notes
Output Gate	OG	-2.5	-2.0	-1.5	V	1 µA	4
Reset Drain	RD	11.5	12.0	12.5	V	1 µA	4
Output Amplifier Supply	VDD	14.5	15.0	15.5	V	1 mA	1
Ground	GND	0.0	0.0	0.0	V		
Substrate	SUB	8.0	Vab	17.0	V		2
ESD Protection	ESD	-9.5	-9.0	-8.0	V		3

Notes:
1. The operating value of the substrate voltage, Vab, will be marked on the shipping container for each device. The value Vab is set such that the photodiode charge capacity is 40,000 electrons.
2. VESD must be equal to FDL and more negative than H1L, H2L and RL during sensors operation *AND* during camera power turn on.
3. One output, unloaded
4. May be changed in future versions.

AC Operating Conditions

Clock Levels

Description	Symbol	Minimum	Nominal	Maximum	Units	Notes
Vertical CCD Clock High	V2H	8.5	9.0	9.5	V	
Vertical CCD Clocks Midlevel	V1M, V2M	-0.5	0.0	0.2	V	
Vertical CCD Clocks Low	V1L, V2L	-9.5	-9.0	-8.5	V	
Horizontal CCD Clocks High	H1H, H2H	0.0	0.5	1.0	V	
Horizontal CCD Clocks Low	H1L, H2L	-5.0	-4.5	-4.0	V	
Reset Clock Amplitude	RH		5.0		V	1
Reset Clock Low	RL	-3.5	-3.0	-2.5	V	2
Electronic Shutter Voltage	Vshutter	44	48	52	V	
Fast Dump High	FDH	4	5	5	V	
Fast Dump Low	FDL	-9.5	-9	-8	V	

Notes:
1. Reset amplitude must be set to 7.0 V for 40,000 electrons output in summed interlaced or binning modes.
2. Reset low level must be set to –5.0 V for 40,000 electrons output in summed interlaced or binning modes.

Clock Line Capacitances

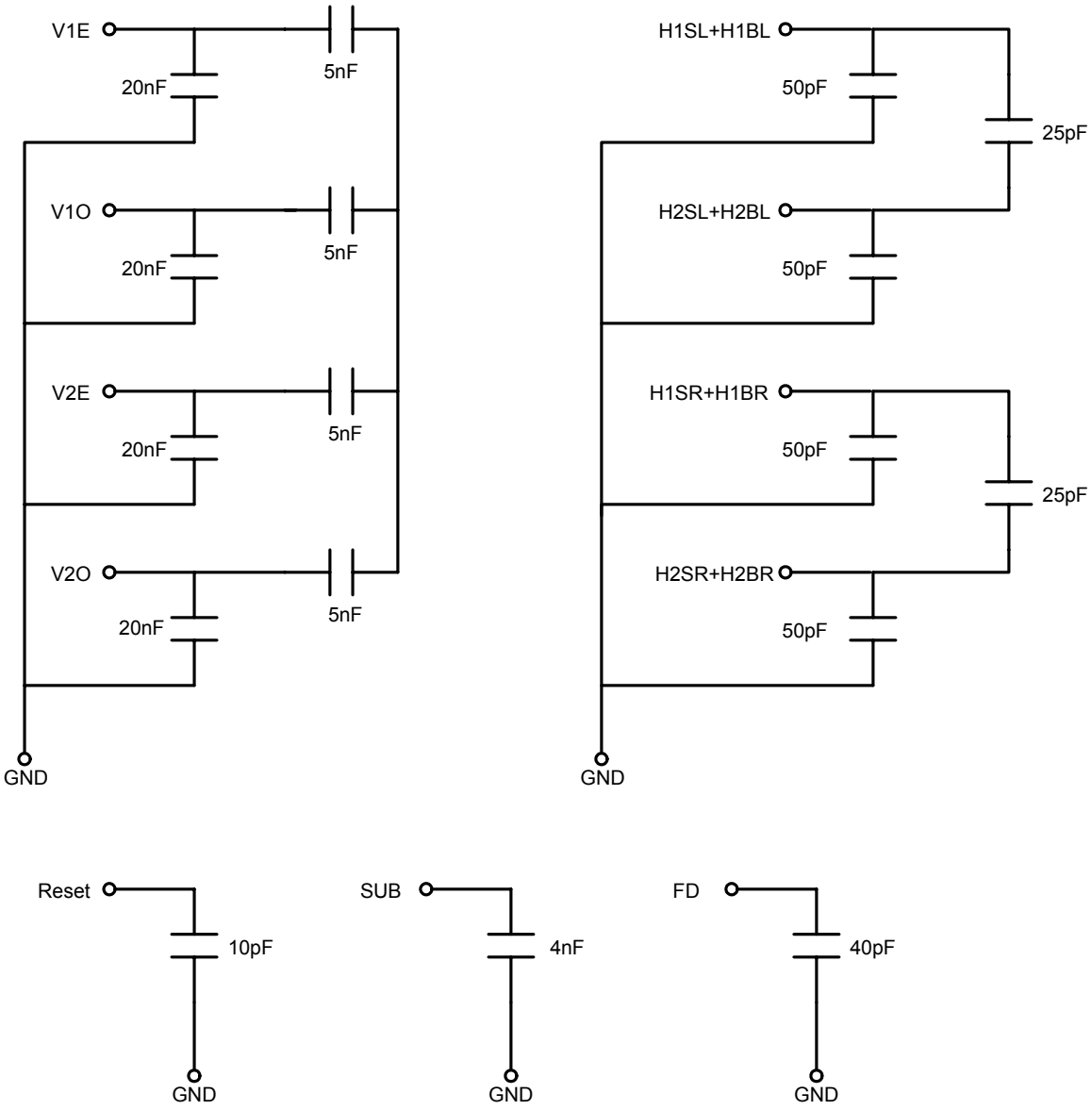


Figure 16 - Clock Line Capacitances

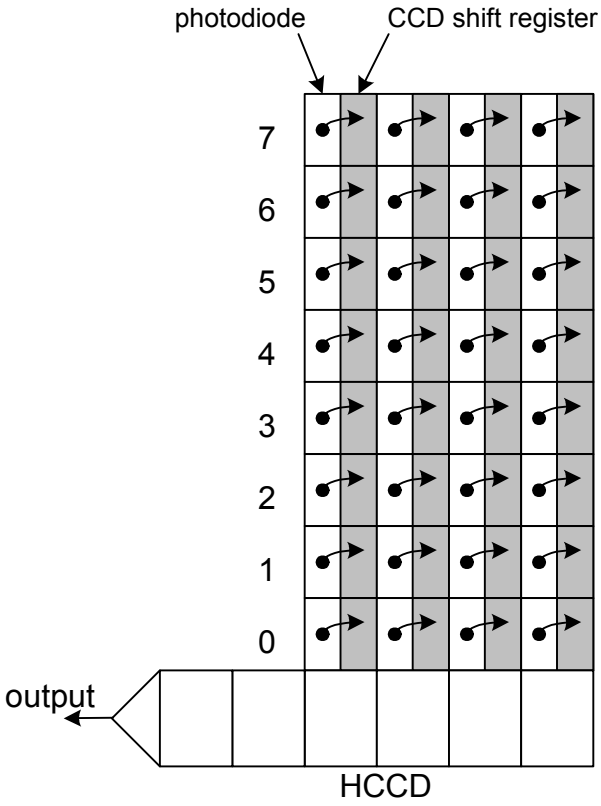
Timing Requirements

Description	Symbol	Minimum	Nominal	Maximum	Units	Notes
HCCD Delay	T_{HD}	1.3	1.5	10.0	µs	
VCCD Transfer time	T_{VCCD}	1.3	1.5	20.0	µs	
Photodiode Transfer time	T_{V3rd}	3.0	5.0	15.0	µs	
VCCD Pedestal time	T_{3P}	50.0	60.0	80.0	µs	
VCCD Delay	T_{3D}	10.0	20.0	80.0	µs	
Reset Pulse time	T_R	2.5	5.0		ns	
Shutter Pulse time	T_S	3.0	4.0	10.0	µs	
Shutter Pulse delay	T_{SD}	1.0	1.5	10.0	µs	
HCCD Clock Period	T_H	25.0	50.0	200.0	ns	1
VCCD rise/fall time	T_{VR}	0.0	0.1	1.0	µs	
Fast Dump Gate delay	T_{FD}	0.5			µs	
Vertical Clock Edge Alignment	T_{VE}	0.0		100.0	ns	

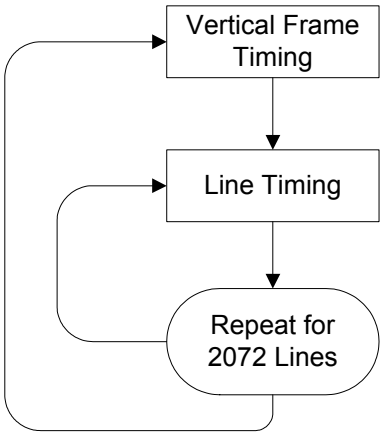
Notes:
1. For operation at the minimum HCCD clock period (40MHz), the substrate voltage will need to be raised to limit the signal at the output to 20,000 electrons.

Timing Modes

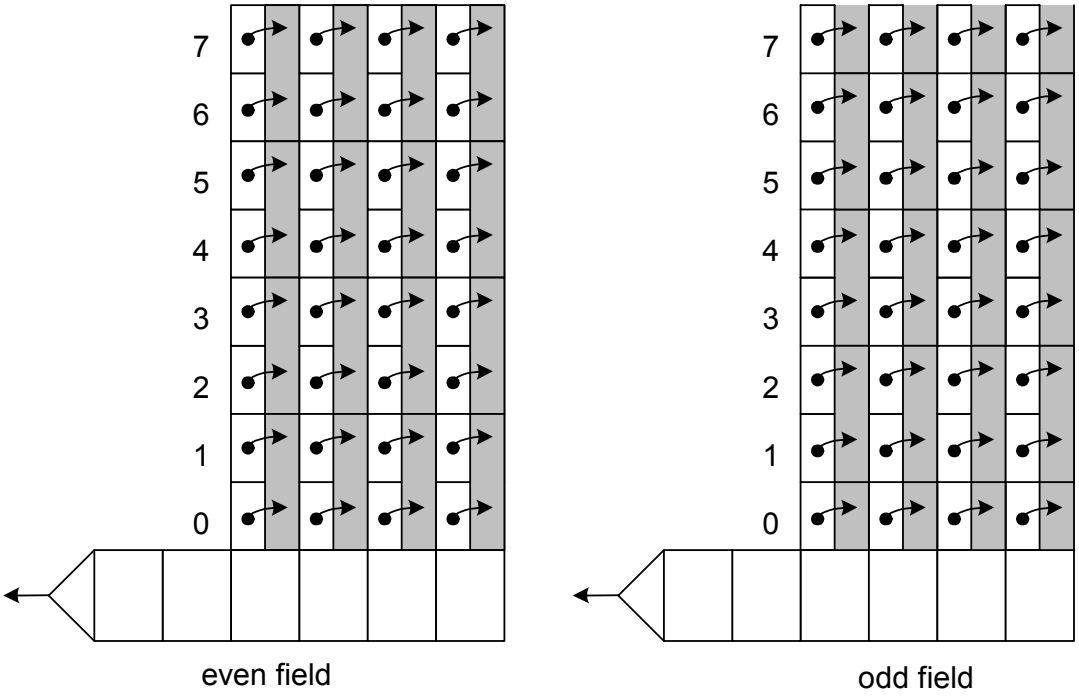
Progressive Scan



In progressive scan read out every pixel in the image sensor is read out simultaneously. Each charge packet is transferred from the photodiode to the neighboring vertical CCD shift register simultaneously. The maximum useful signal output is limited by the photodiode charge capacity to 40,000 electrons.

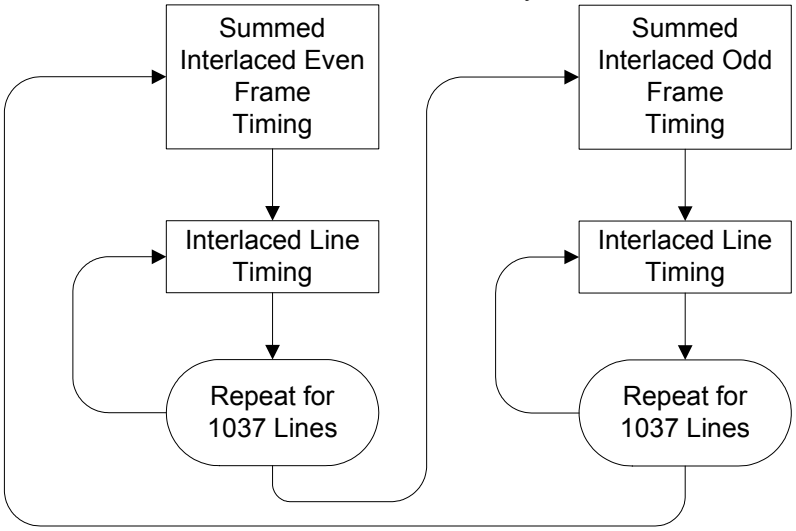


Summed Interlaced Scan

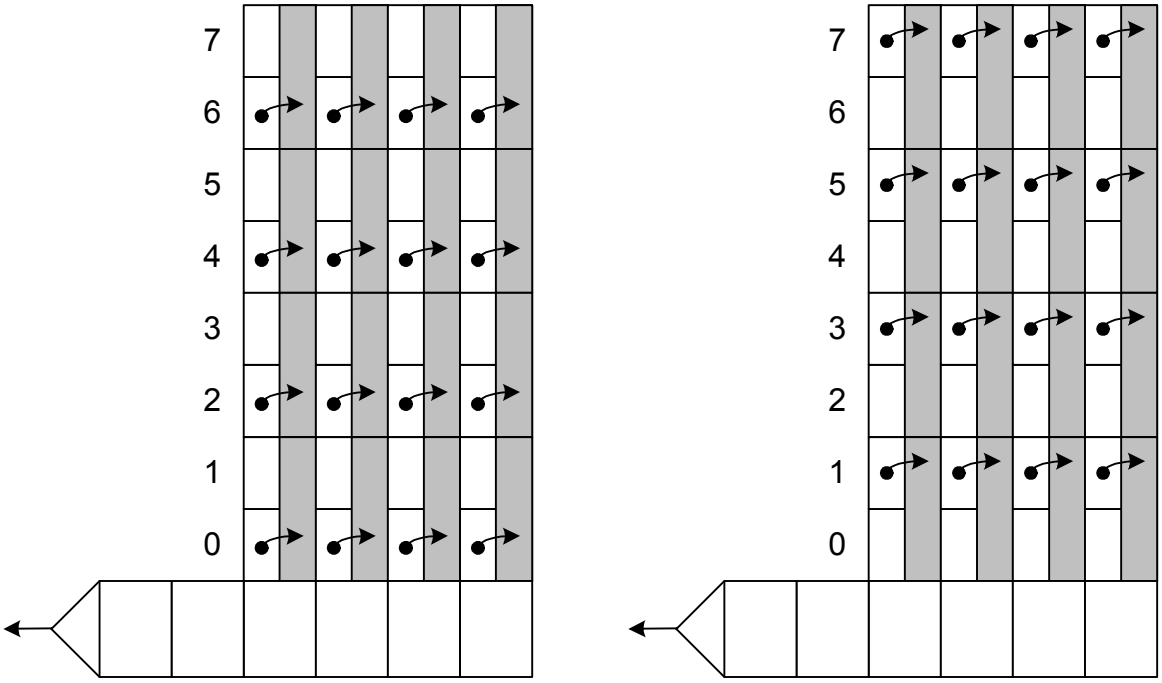


In the summed interlaced scan read out mode, charge from two photodiodes are summed together inside the vertical CCD. The clocking of the VCCD is such that one pixel occupies the space equivalent to two pixels in the progressive scan mode. This allows the VCCD to hold twice as many electrons as in progressive scan mode. Now the maximum useful signal is limited by the charge capacity of two photodiodes at 80,000 electrons. If only one field is read out of the image sensor the apparent vertical resolution will be 1024 rows instead of the 2048 rows in progressive scan (equivalent to binning). To recover the full resolution of the image sensor two fields, even and odd, are read out. In the even field rows 0+1, 2+3, 4+5, … are summed together. In the odd field rows 1+2, 3+4, 5+6, … are summed together.

The modulation transfer function (MTF) of the summed interlaced scan mode is less in the vertical direction than the progressive scan. But the dynamic range is twice that of progressive scan. The vertical MTF is better than a simple binning operation. In this mode the VCCD needs to be clocked for only 1037 rows to read out each field.

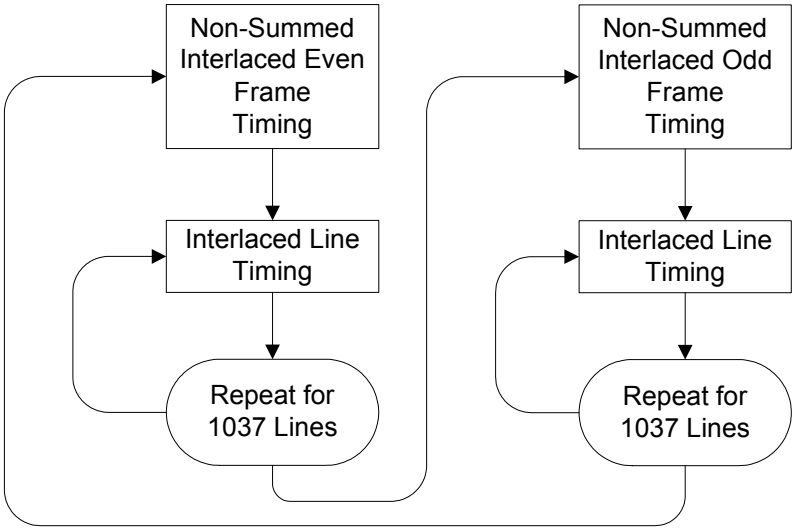


Non-Summed Interlaced Scan



even field odd field

In the non-summed interlaced scan mode only half the photodiode are read out in each field. In the even field rows 0, 2, 4, … are transferred to the VCCD. In the odd field rows 1, 3, 5, … are transferred to the VCCD. When the charge packet is transferred from a photodiode is occupies the equivalent of two rows in progressive scan mode. This allows the VCCD to hold twice as much charge a progressive scan mode. However, since only one photodiode for each row is transferred to the VCCD the maximum usable signal is still only 40,000 electrons. The large extra capacity of the VCCD causes the anti-blooming protection to be increased dramatically compared to the progressive scan. The vertical MTF is the same between the non-summed interlaced scan and progressive scan. There will be motion related artifacts in the images read out in the interlaced modes because the two fields are acquired at different times.



Frame Timing

Frame Timing without Binning - Progressive Scan

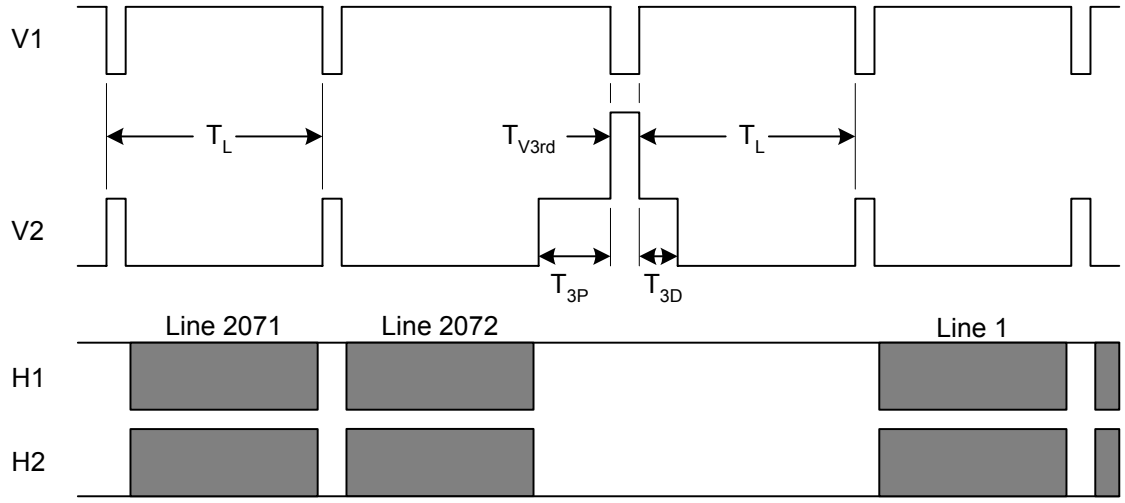


Figure 17 - Framing Timing without Binning

Frame Timing for Vertical Binning by 2 - Progressive Scan

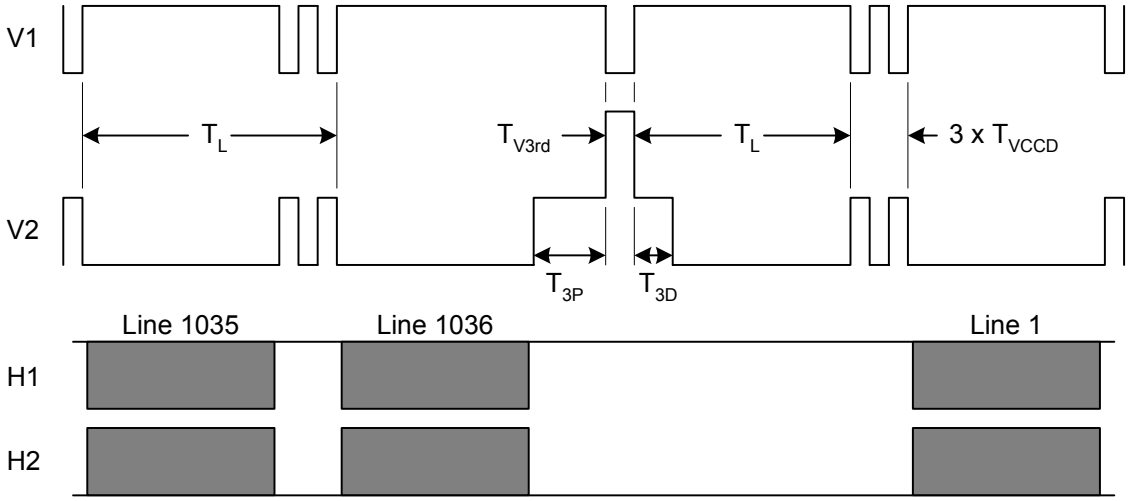


Figure 18 - Frame Timing for Vertical Binning by 2

Frame Timing Non-Summed Interlaced Scan

Even Frame Non Summed Interlaced Scan

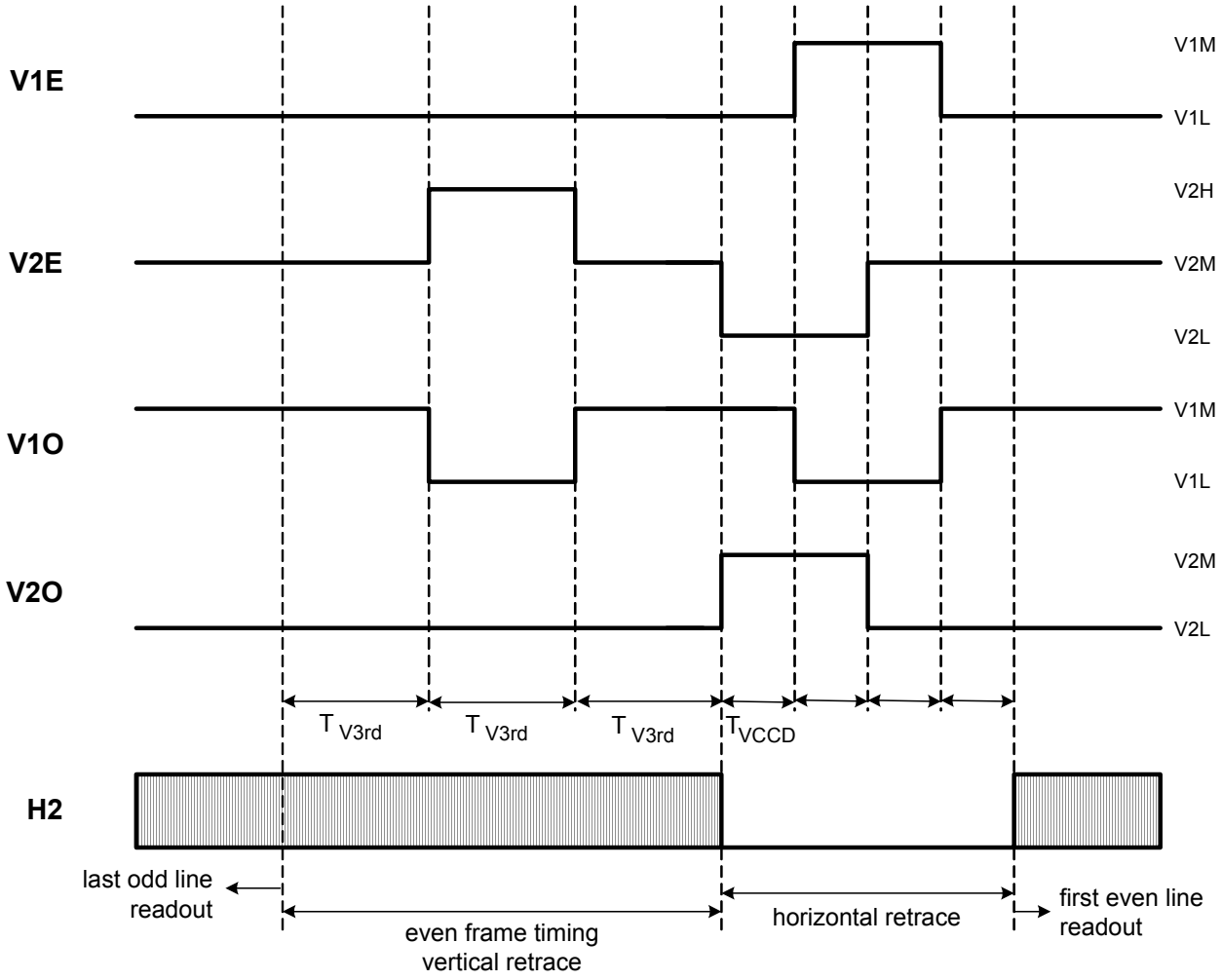


Figure 19 - Non-Summed Interlaced Scan Even Frame Timing

Odd Frame Non-Summed Interlaced Scan

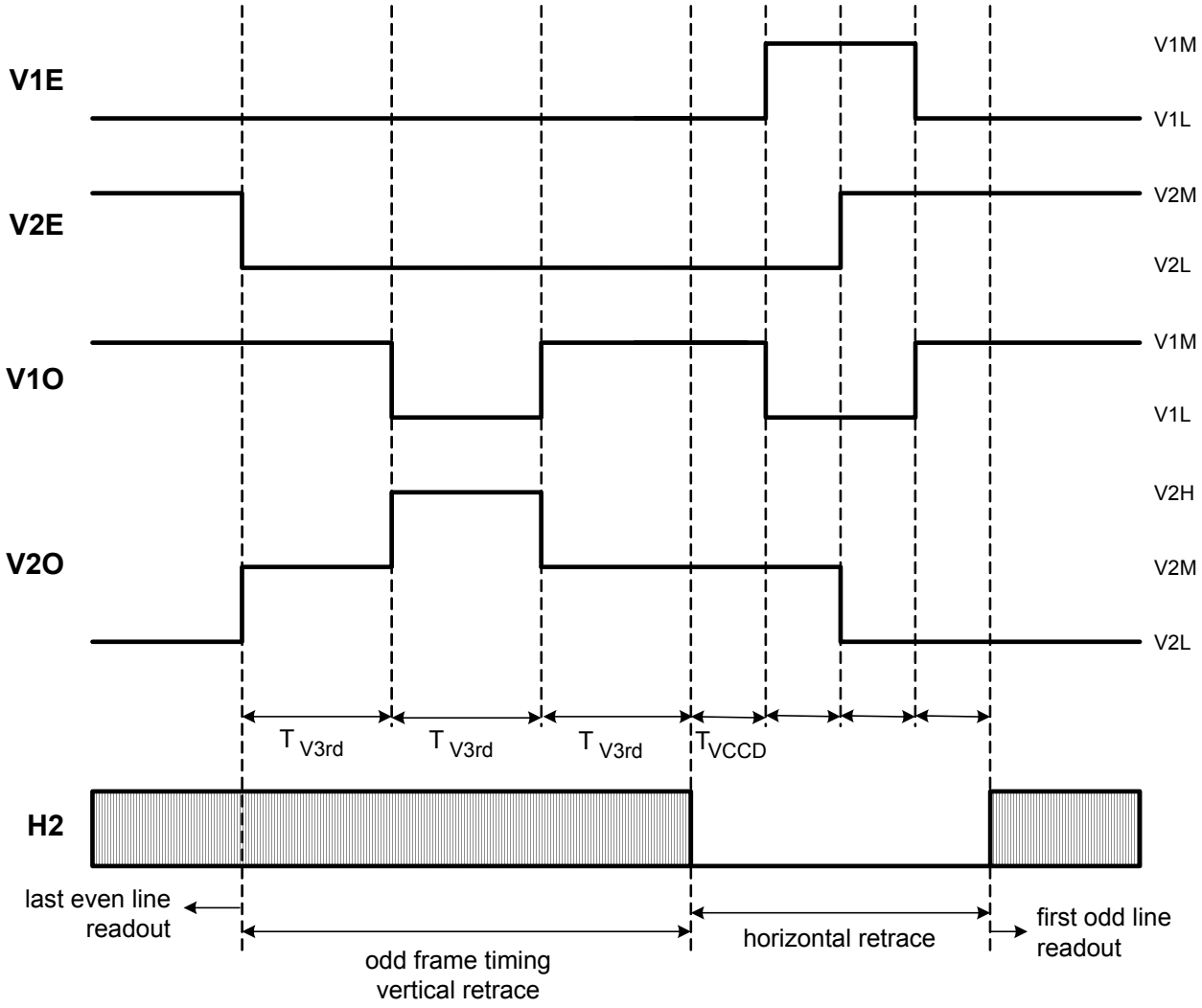


Figure 20 - Non-Summed Interlaced Scan Odd Frame Timing

Frame Timing Summed Interlaced Scan

Even Frame Summed Interlaced Scan

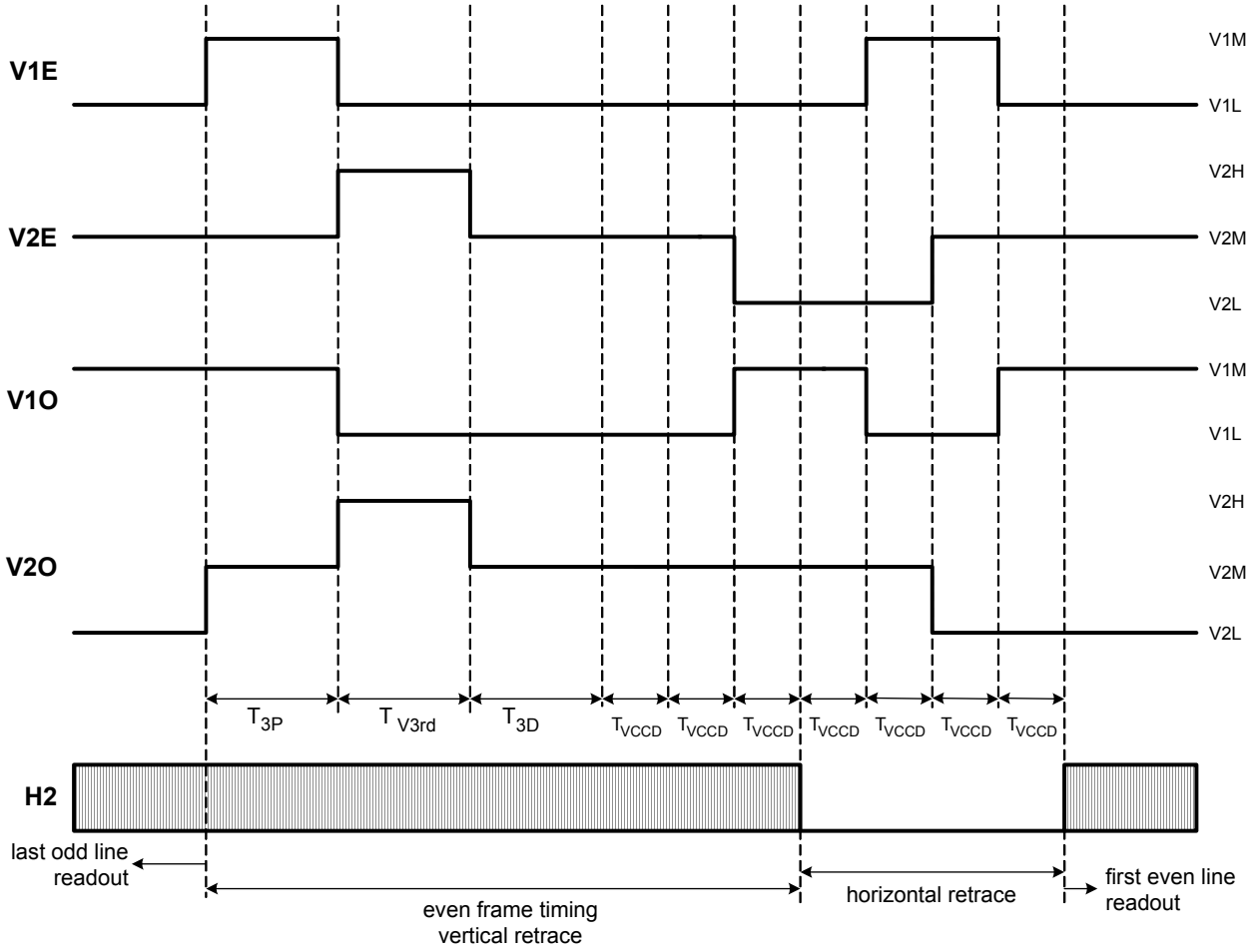


Figure 21 - Summed Interlaced Scan Even Frame Timing

Odd Frame Summed Interlaced Scan

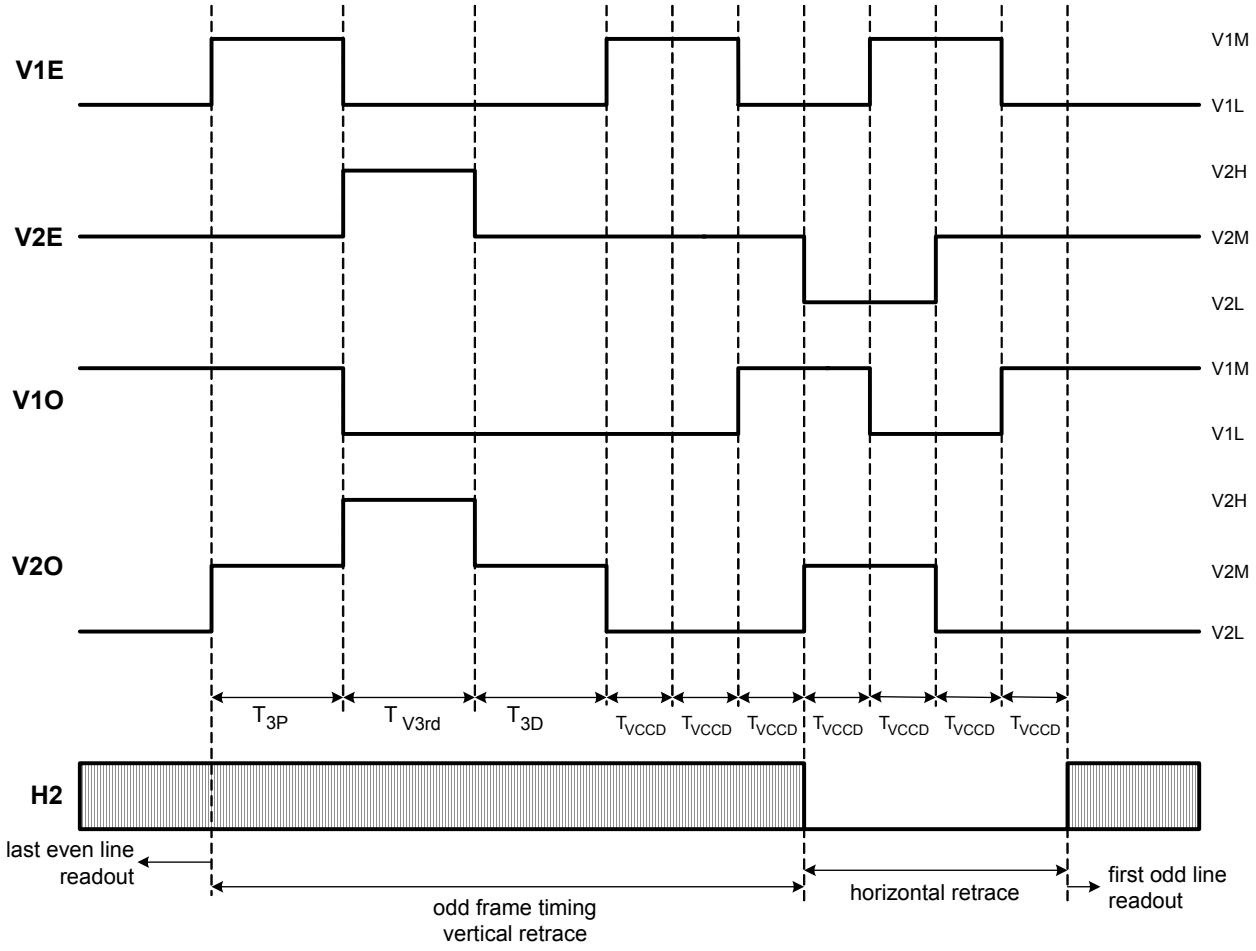


Figure 22 - Summed Interlaced Scan Odd Frame Timing

Frame Timing Edge Alignment

Applies to all modes.

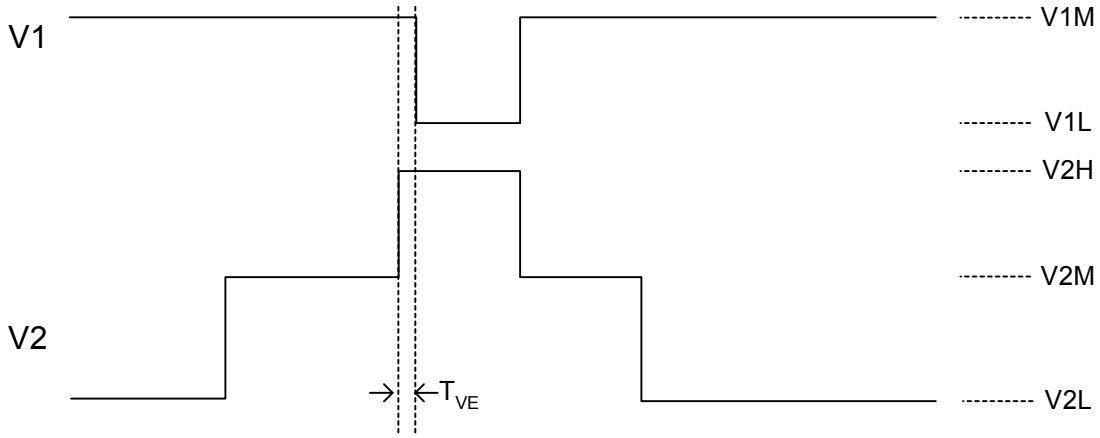


Figure 23 - Frame Timing Edge Alignment

Line Timing

Line Timing Single Output – Progressive Scan

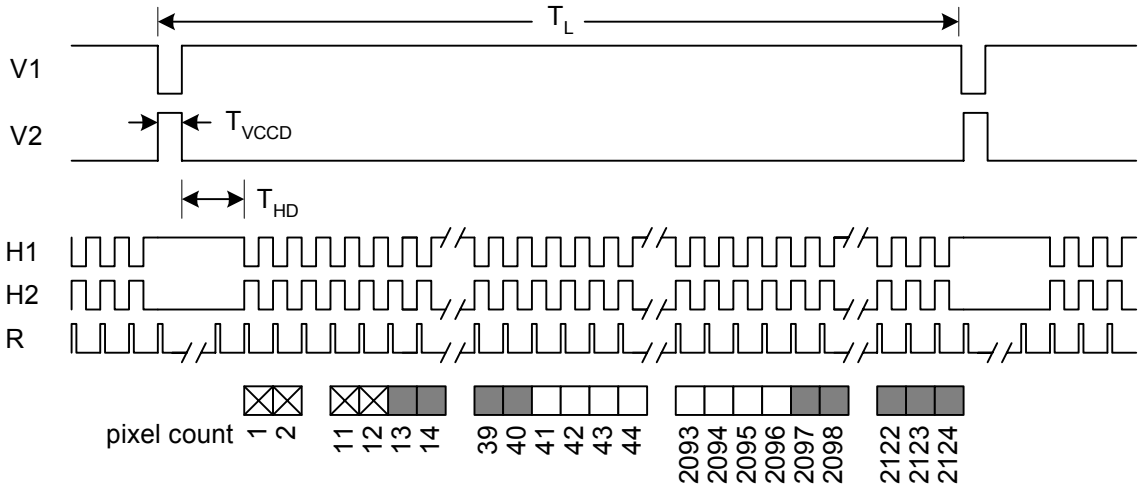


Figure 24 - Line Timing Single Output

Line Timing Dual Output – Progressive Scan

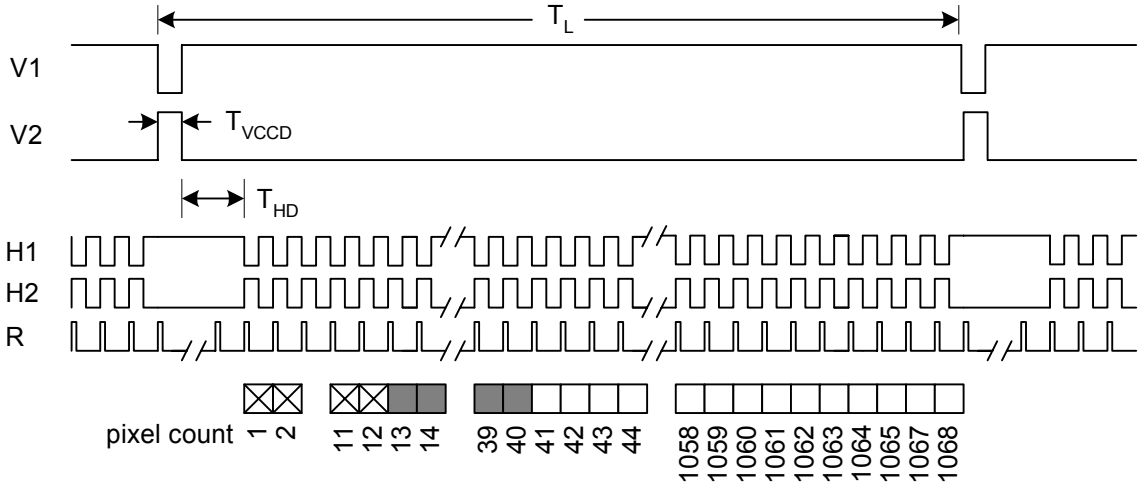


Figure 25 - Line Timing Dual Output

Line Timing Vertical Binning by 2 – Progressive Scan

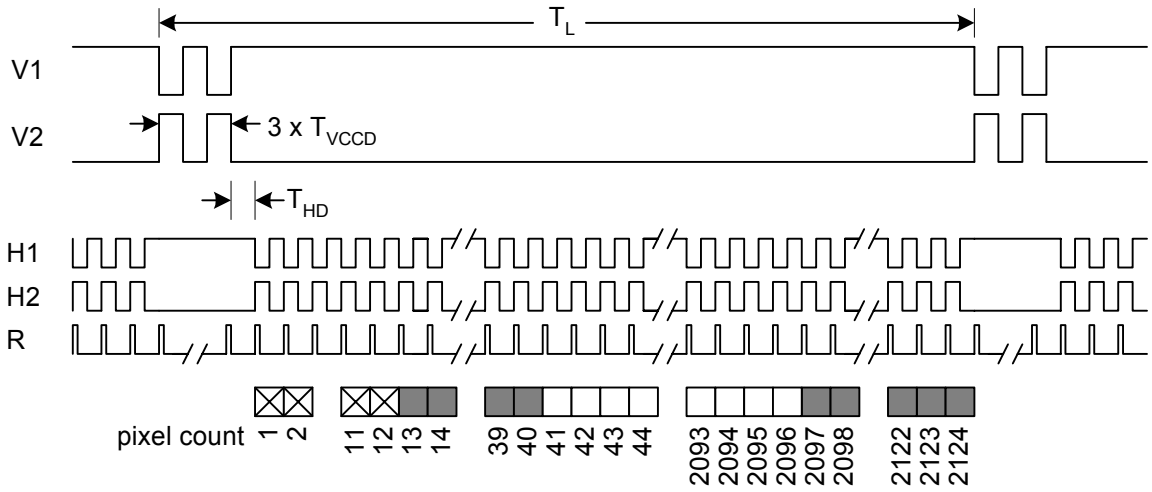


Figure 26 - Line Timing Vertical Binning by 2

Line Timing Detail – Progressive Scan

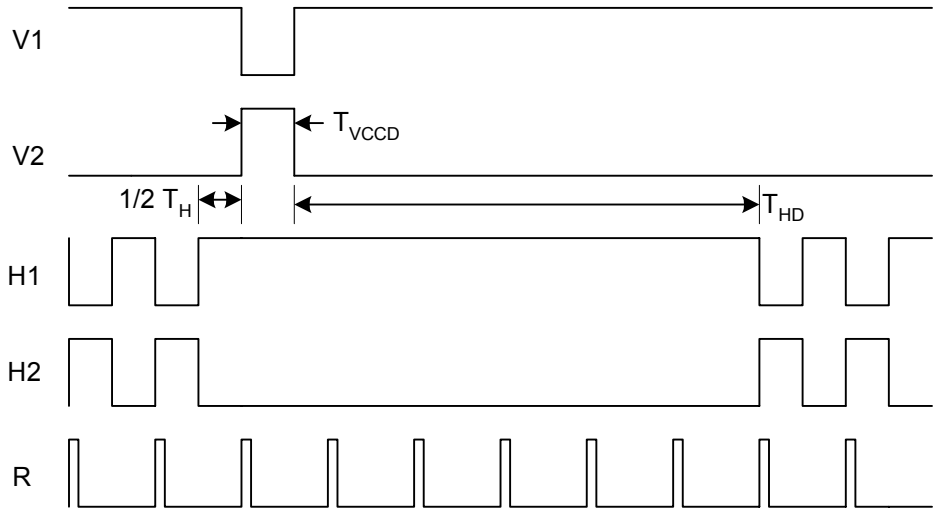


Figure 27 - Line Timing Detail

Line Timing Binning by 2 Detail – Progressive Scan

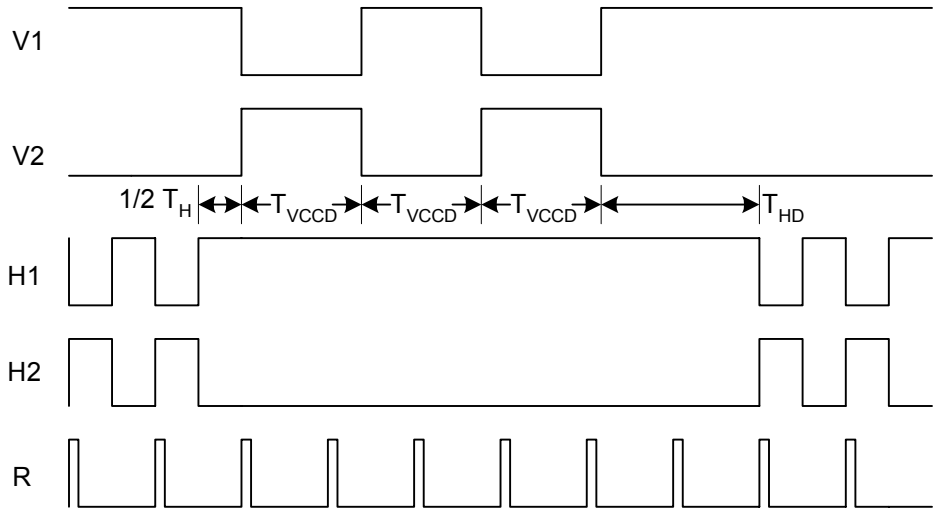


Figure 28 - Line Timing by 2 Detail

Line Timing Interlaced Modes

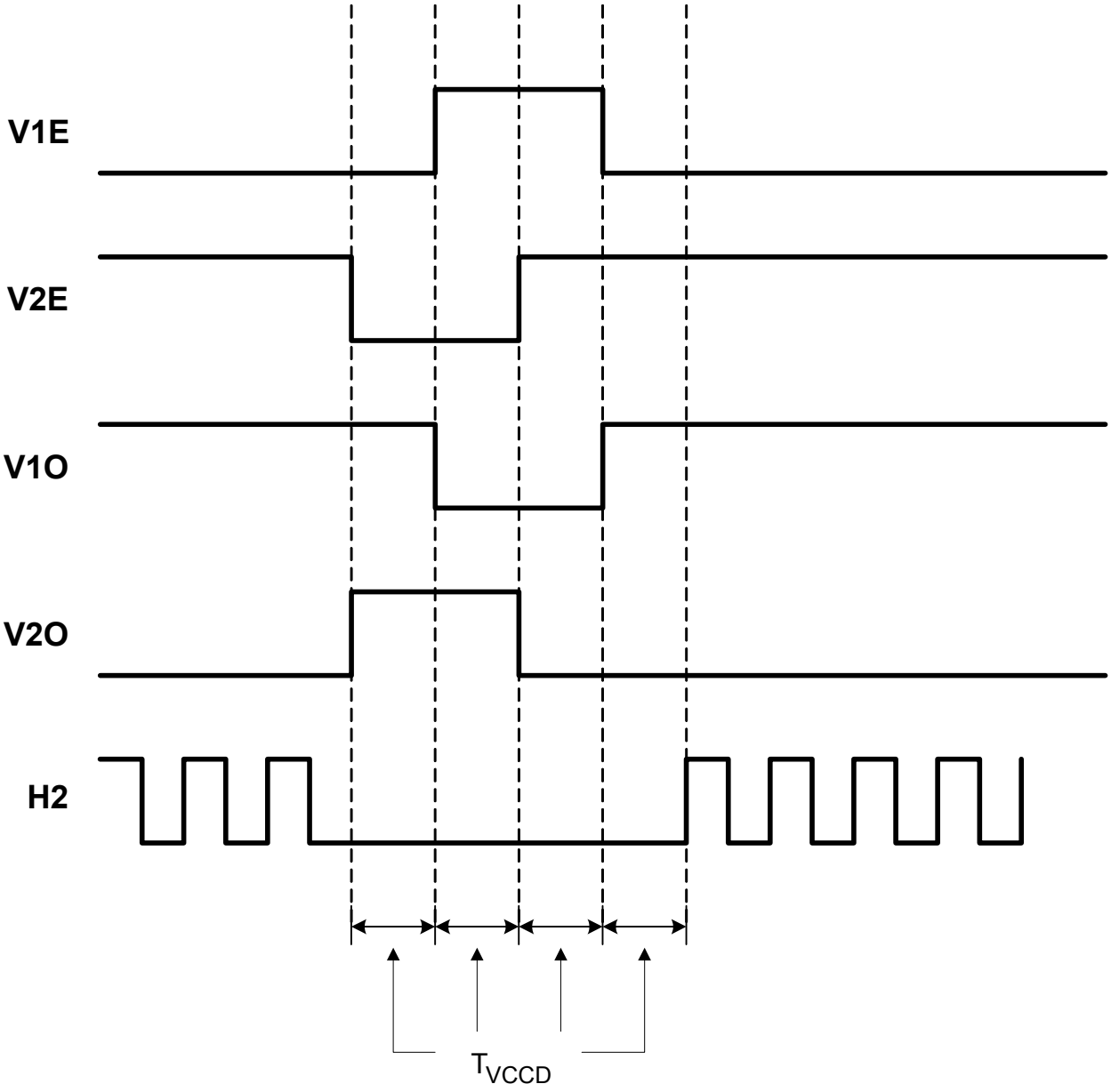


Figure 29 - Line Timing Interlaced Modes

Line Timing Edge Alignment

Applies to all modes.

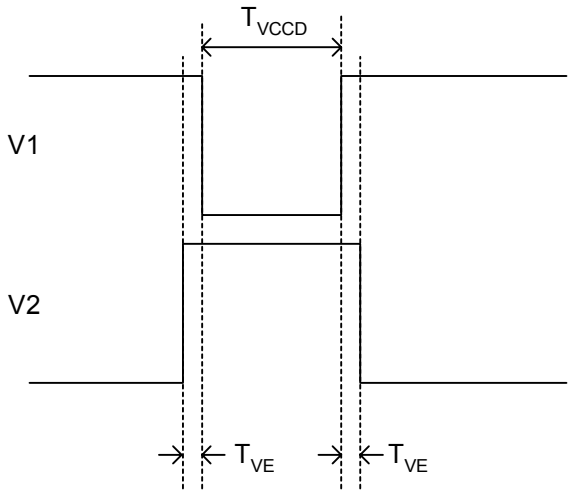


Figure 30 - Line Timing Edge Alignment

Pixel Timing

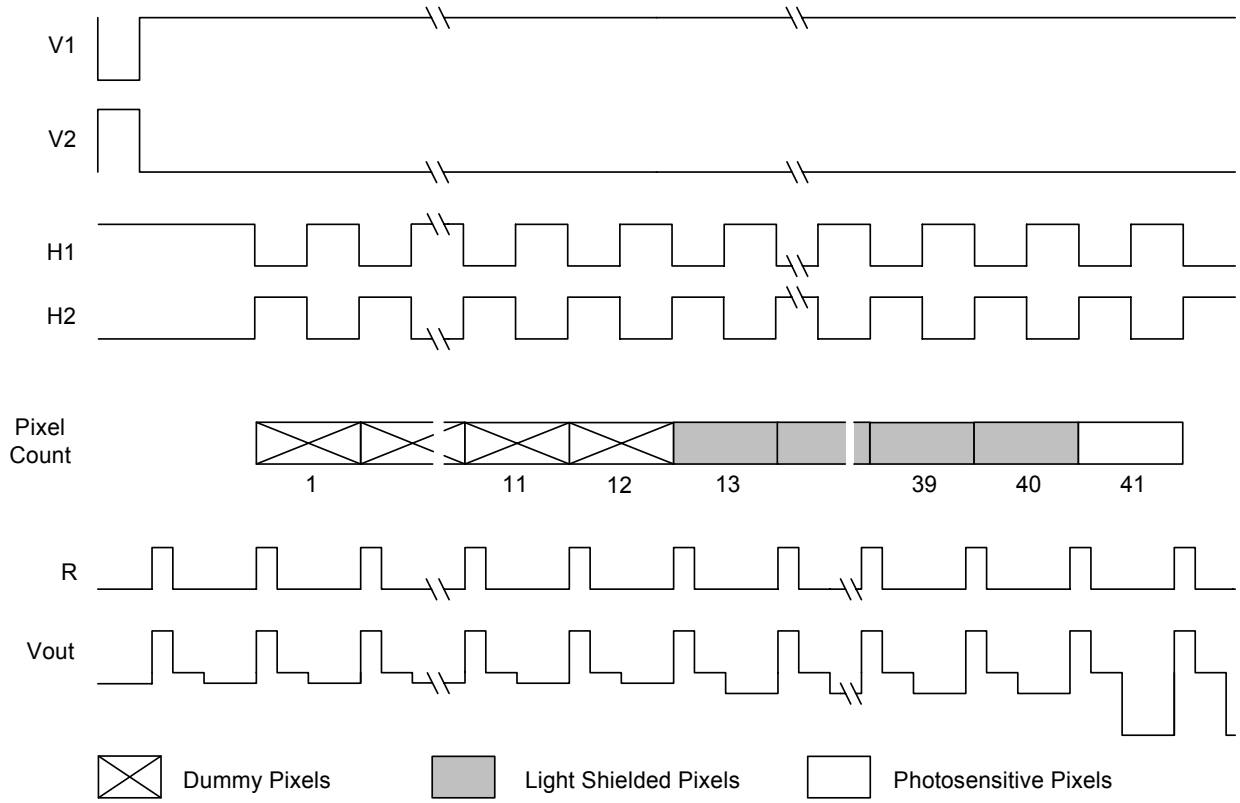


Figure 31 - Pixel Timing

Pixel Timing Detail

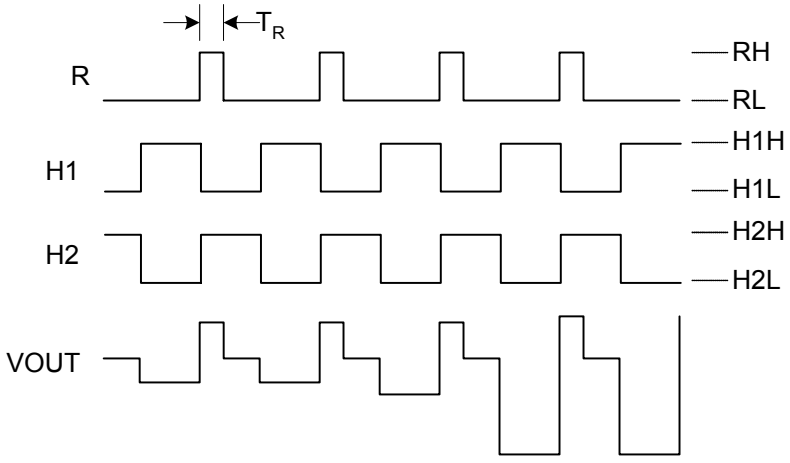


Figure 32 - Pixel Timing Detail

Fast Line Dump Timing

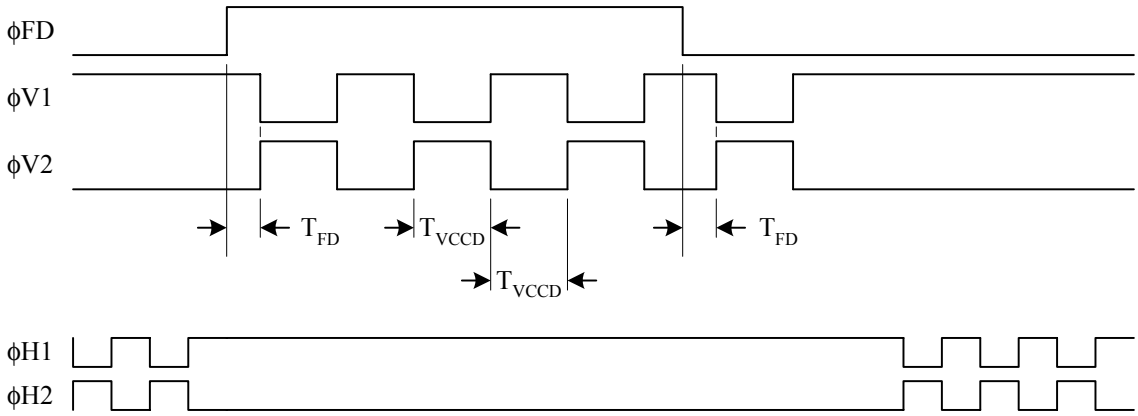


Figure 33 - Fast Line Dump Timing

Electronic Shutter

Electronic Shutter Line Timing

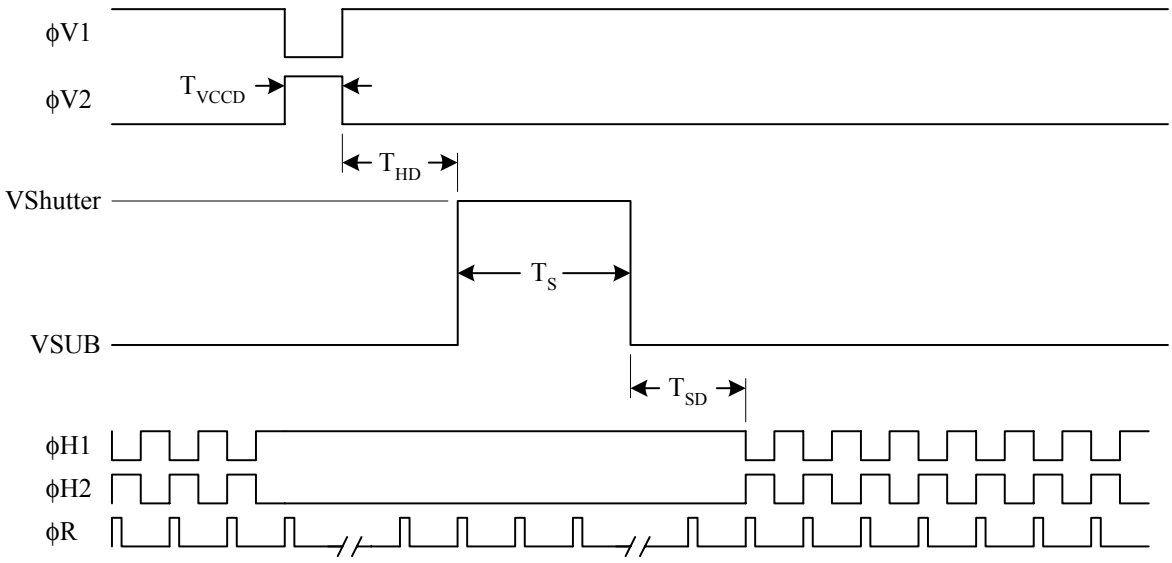


Figure 34 - Electronic Shutter Line Timing

Electronic Shutter – Integration Time Definition

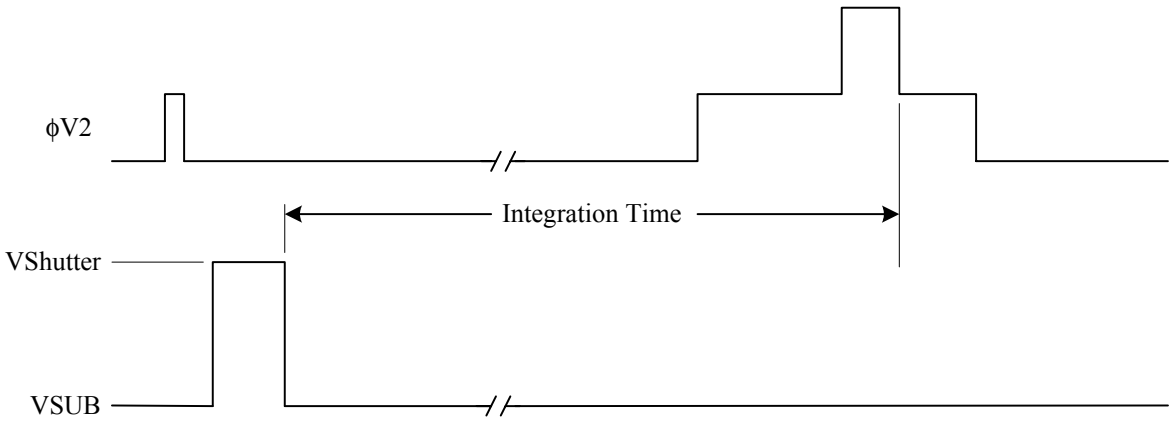


Figure 35 - Integration Time Definition

Electronic Shutter Description

The voltage on the substrate (SUB) determines the charge capacity of the photodiodes. When SUB is 8 volts the photodiodes will be at their maximum charge capacity. Increasing VSUB above 8 volts decreases the charge capacity of the photodiodes until 48 volts when the photodiodes have a charge capacity of zero electrons. Therefore, a short pulse on SUB, with a peak amplitude greater than 48 volts, empties all photodiodes and provides the electronic shuttering action.

It may appear the optimal substrate voltage setting is 8 volts to obtain the maximum charge capacity and dynamic range. While setting VSUB to 8 volts will provide the maximum dynamic range, it will also provide the minimum antiblooming protection.

The KAI-4020 VCCD has a charge capacity of 60,000 electrons (60 ke^-). If the SUB voltage is set such that the photodiode holds more than 60 ke^-, then when the charge is transferred from a full photodiode to VCCD, the VCCD will overflow. This overflow condition manifests itself in the image by making bright spots appear elongated in the vertical direction. The size increase of a bright spot is called blooming when the spot doubles in size. The blooming can be eliminated by increasing the voltage on SUB to lower the charge capacity of the photodiode. This ensures the VCCD charge capacity is greater than the photodiode capacity. There are cases where an extremely bright spot will still cause blooming in the VCCD. Normally, when the photodiode is full, any additional electrons generated by photons will spill out of the photodiode. The excess electrons are drained harmlessly out to the substrate. There is a maximum rate at which the electrons can be drained to the substrate. If that maximum rate is exceeded, (for example, by a very bright light source) then it is possible for the total amount of charge in the photodiode to exceed the VCCD capacity. This results in blooming. The amount of antiblooming protection also decreases when the integration time is decreased. There is a compromise between photodiode dynamic range (controlled by VSUB) and the amount of antiblooming protection. A low VSUB voltage provides the maximum dynamic range and minimum (or no) antiblooming protection. A high VSUB voltage provides lower dynamic range and maximum antiblooming protection. The optimal setting of VSUB is written on the container in which each KAI-4020 is shipped. The given VSUB voltage for each sensor is selected to provide antiblooming protection for bright spots at least 100 times saturation, while maintaining at least 40 ke^- of dynamic range.

The electronic shutter provides a method of precisely controlling the image exposure time without any mechanical components. If an integration time of T_{INT} is desired, then the substrate voltage of the sensor is pulsed to at least 40 volts T_{INT} seconds before the photodiode to VCCD transfer pulse on V2. Use of the electronic shutter does not have to wait until the previously acquired image has been completely read out of the VCCD.

Large Signal Output

When the image sensor is operated in the binned or summed interlaced modes there will be more than 20,000 electrons in the output signal. The image sensor is designed with a 31µV/e charge to voltage conversion on the output. This means a full signal of 20,000 electrons will produce a 640 mV change on the output amplifier. The output amplifier was designed to handle an output swing of 640 mV at a pixel rate of 40 MHz. If 40,000 electron charge packets are generated in the binned or summed interlaced modes then the output amplifier output will have to swing 1280 mV. The output amplifier does not have enough bandwidth (slew rate) to handle 1280 mV at 40 MHz. Hence, the pixel rate will have to be reduced to 20 MHz if the full dynamic range of 40,000 electrons is desired.

The charge handling capacity of the output amplifier is also set by the reset clock voltage levels. The reset clock driver circuit is very simple if an amplitude of 5 V is used. But the 5 V amplitude restricts the output amplifier charge capacity to 20,000 electrons. If the full dynamic range of 40,000 electrons is desired then the reset clock amplitude will have to be increased to 7 V.
If you only want a maximum signal of 20,000 electrons in binned or summed interlaced modes, then a 40 MHz pixel rate with a 5 V reset clock may be used. The output of the amplifier will be unpredictable above 20,000 electrons so be sure to set the maximum input signal level of your analog to digital converter to the equivalent of 20,000 electrons (640 mV).

STORAGE AND HANDLING

Storage Conditions

Description	Symbol	Minimum	Maximum	Units	Notes
Temperature	T	-55	80	°C	1
Humidity	RH	5	90	%	2

Notes:
1. Long-term exposure toward the maximum temperature will accelerate color filter degradation.
2. T=25ºC. Excessive humidity will degrade MTTF.

Soldering Recommendations

1. The soldering iron tip temperature is not to exceed 370ºC. Failure to do so may alter device performance and reliability.
2. Flow soldering method is not recommended. Solder dipping can cause damage to the glass and harm the imaging capability of the device. Recommended method is by partial heating. Kodak recommends the use of a grounded 30W soldering iron. Heat each pin for less than 2 seconds duration.

MECHANICAL DRAWINGS

Package

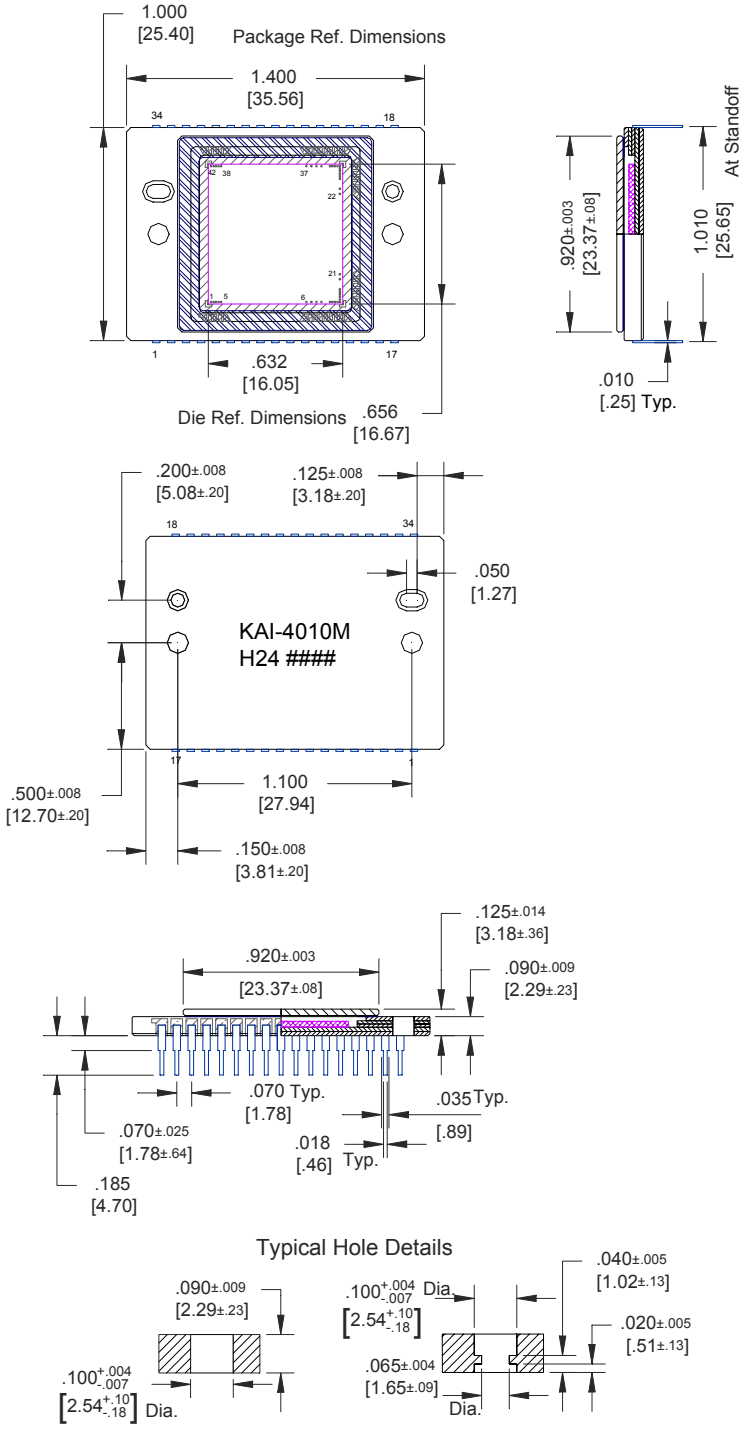
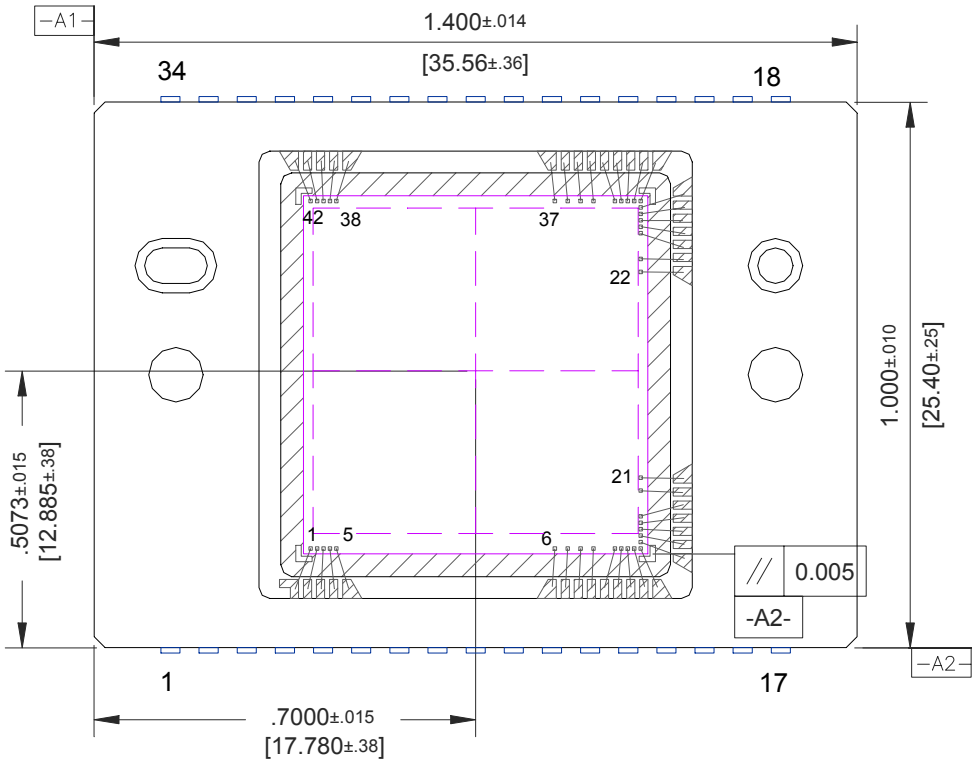


Figure 36 - Package Drawing

Die to Package Alignment



Notes:

1)Center of image is offset from center of package by (0.000, 0.185)mm nominal.

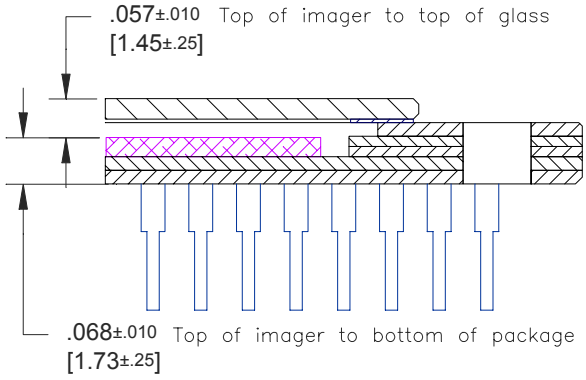


Figure 37 - Die to Package Alignment

Glass

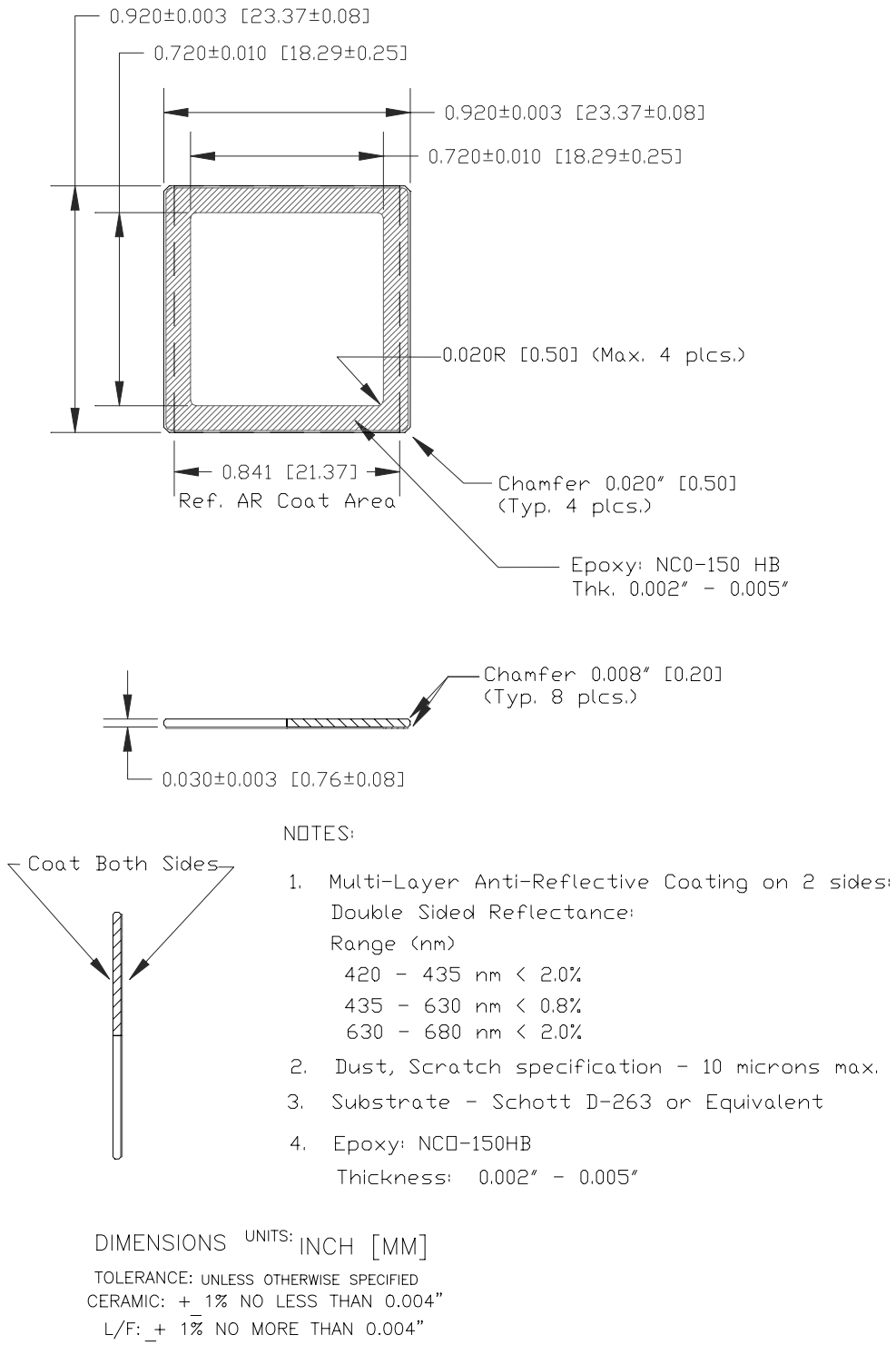


Figure 38 - Glass Drawing

Glass Transmission

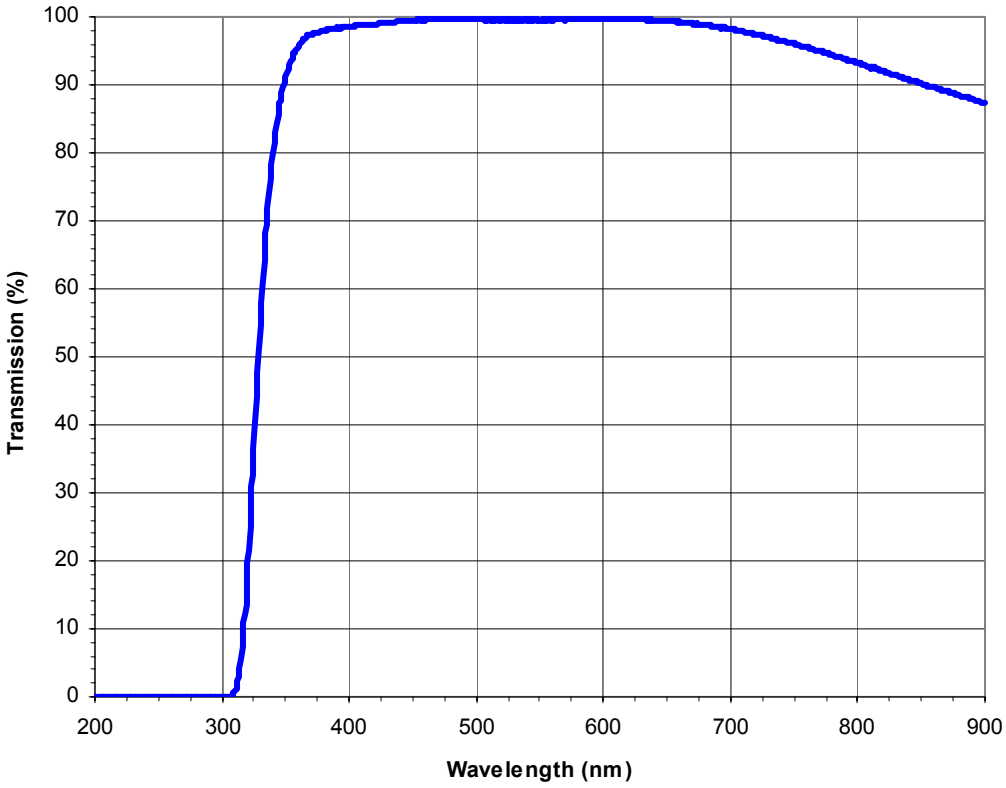


Figure 39 - Glass Transmission

QUALITY ASSURANCE AND RELIABILITY

Quality Strategy: All image sensors will conform to the specifications stated in this document. This will be accomplished through a combination of statistical process control and inspection at key points of the production process. Typical specification limits are not guaranteed but provided as a design target. For further information refer to ISS Application Note MTD/PS-0292, Quality and Reliability.

Replacement: All devices are warranted against failure in accordance with the terms of Terms of Sale. This does not include failure due to mechanical and electrical causes defined as the liability of the customer below.

Liability of the Supplier: A reject is defined as an image sensor that does not meet all of the specifications in this document upon receipt by the customer.

Liability of the Customer: Damage from mechanical (scratches or breakage), electrostatic discharge (ESD) damage, or other electrical misuse of the device beyond the stated absolute maximum ratings, which occurred after receipt of the sensor by the customer, shall be the responsibility of the customer.

Cleanliness: Devices are shipped free of mobile contamination inside the package cavity. Immovable particles and scratches that are within the imager pixel area and the corresponding cover glass region directly above the pixel sites are also not allowed. The cover glass is highly susceptible to particles and other contamination. Touching the cover glass must be avoided. See ISS Application Note MTD/PS-0237, Cover Glass Cleaning for Image Sensors, for further information.

ESD Precautions: Devices are shipped in static-safe containers and should only be handled at static-safe workstations. See ISS Application Note MTD/PS-0224, Electrostatic Discharge Control, for handling recommendations.

Reliability: Information concerning the quality assurance and reliability testing procedures and results are available from the Image Sensor Solutions and can be supplied upon request. For further information refer to ISS Application Note MTD/PS-0292, Quality and Reliability.

Test Data Retention: Image sensors shall have an identifying number traceable to a test data file. Test data shall be kept for a period of 2 years after date of delivery.

Mechanical: The device assembly drawing is provided as a reference. The device will conform to the published package tolerances.

ORDERING INFORMATION

Available Part Configurations

Type	Description	Glass Configuration
KAI-4020	Monochrome	Taped
KAI-4020M	Monochrome with microlens	Sealed or Taped
KAI-4020CM	Color with microlens	Sealed

Please contact Image Sensor Solutions for available part numbers.

Address all inquiries and purchase orders to:

Image Sensor Solutions
Eastman Kodak Company
Rochester, New York 14650-2010
Phone: (585) 722-4385
Fax: (585) 477-4947
E-mail: imagers@kodak.com

WARNING: LIFE SUPPORT APPLICATIONS POLICY

Kodak image sensors are not authorized for and should not be used within Life Support Systems without the specific written consent of the Eastman Kodak Company. Product warranty is limited to replacement of defective components and does not cover injury or property or other consequential damages.

REVISION CHANGES

Revision Number	Description of Changes
1.0	Initial formal release.
2.0	Page 6 – added notes with regard to the use of dark rows and columns. Page 16 – corrected noise specifications. Page 18 – corrected minor and major dark field defect definitions – descriptions were swapped and incorrect. Values were from KAI-4010 specification, which has half the gain. Page 25 – revised note 4. Added note 4 to reset drain description Page 26 – changed 80,00 electrons to 40,000 electrons in Notes 1 and 2 of the AC Operating Conditions, Clock Levels table.